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(54) LIGHT-EMITTING DIODE

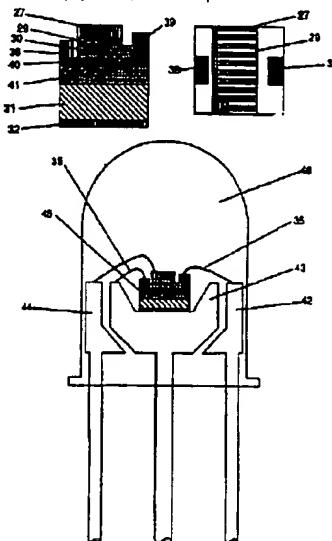
LED whose performance is stable can be supplied.

(57) Abstract:

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PURPOSE: To obtain an LED provided with a good light-emitting characteristic by using a wire bonding method when all electrodes for an element chip using an insulating substrate are connected to individual lead members.

CONSTITUTION: Individual chips are cut by using a dicing saw, one chip is taken out, the side of a reflection film 32 is die-bonded to a lead member 43 by using a Pb-Sn solder, electrodes for an n-type GaN layer 30 and an n-type $Ga_{0.8}In_{0.2}N$ layer 41 are connected by $30\mu m$ ϕ Au wires 35 by using a wire bonding apparatus. Then, an i-type GaN layer electrode 27 is connected to a lead member 44 and an i-type $Ga_{0.8}In_{0.2}N$ layer electrode 38 is connected to a lead member 43 respectively by $30\mu m$ ϕ Au wires 35 by using the wire bonding apparatus, and a manufactured light-emitting element 46 is sealed with a transparent epoxy resin. Consequently, all electrodes formed inside the same plane can be connected individually to lead members divided into the same number as the number of electrodes by using a wire bonding method. Thereby, an



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CLAIMS

[Claim(s)]

[Claim 1] Light emitting diode characterized by the structure where all connection wiring with an electrode and a lead member is wires, in the element chip of the planar structure which has an electrode for having at least one luminous layer which consists of two or more sorts of combination chosen from the n-type-semiconductor layer, p type, and the i-type-semiconductor layer on the insulating substrate, and impressing voltage to the predetermined part of a semiconductor layer at a luminous layer.

DETAILED DESCRIPTION

[Detailed Description of the Invention]

[0001]

[Industrial Application] this invention relates to the light emitting diode which mounted the light-emitting-device chip which used the insulating substrate in the leadframe.

[0002]

[Description of the Prior Art] Since the element chip conventionally mounted in the light emitting diode (Light Emitting Diode) put in practical use used conductive substrates, such as GaAs and InP, the polar zone of positive/negative was formed in the table and the reverse side of an element chip. The cross section of Light Emitting Diode which mounted the element chip in the conventional leadframe and was closed by the resin is shown in drawing 12 . the case where this element chip 24 is pasted up on a leadframe 49 since the element chip produced using the conductive substrate has taken the structure of having an electrode on a table and the reverse side as mentioned above -- one of the two's electrode -- the mirror section 50 of a leadframe -- a pewter or a conductive paste -- pasting up -- already -- one of the two's electrode -- the wire-bonding method -- a lead -- structure which is connected to a member 48 was taken this lead -- after mounting an element chip in members 47 and 48, it closed by the epoxy resin etc. and Light Emitting Diode25 was formed In recent years, Light Emitting Diode by the element chip of the flip chip method which used the transparent insulation substrate is proposed. (JP,4-10670,A) structure as shown in drawing 13 as a Light Emitting Diode produced using the light-emitting-device chip in which the luminous layer was formed on this transparent insulation substrate -- it is -- the electrodes 19 and 20 of the element chip 24 -- the electrode of positive/negative -- a luminous layer side -- being located -- a lead -- connection with members 51 and 52 was made with a pewter or a conductive paste

[0003]

[Problem(s) to be Solved by the Invention] Since current can be passed to a substrate when a conductive substrate is used for a light-emitting-device chip, as mentioned above, the electrode of positive/negative can be formed in a substrate side at one one and luminous layer side. Carrying out die bonding of the electrode by the side of a substrate to the lead member, when connecting with a leadframe, the electrode by the side of a luminous layer was producing Light Emitting Diode by the method of carrying out wire bonding to other lead members. when a transparent insulation substrate is used for an element chip, in order [however,] to take the flip chip method which has the electrode of a positive/negative couple in a luminous layer side -- an element chip and a lead -- connection of a member cannot take the connection method mentioned above for this reason -- in order to connect to a leadframe two sorts of electrodes formed in the luminous layer side -- the lead of two -- the connection side with the

element chip of a member is made flat, and the process which pastes up the electrode side of an element chip on this flat side with a pewter or a conductive paste is taken. However, by this method, in order to have to form two sorts of electrodes in the same field, in the element chip size below 1mm angle, electrode size had the problem that two sorts of electrode sections will contact in an according [if it kicks, will not become but] to pewter or conductive paste adhesion [carry out] process, with 200 micrometers or less. Moreover, since the electrode area pasted up with the pewter or the conductive paste to an element chip size was large, a complicated electrode pattern like the shape of the shape of MIANDA used in order to make light emit more efficiently, the letter of a network, or CUSH was not able to be formed. Or when producing the multicolor light emitting diode which obtains luminescence of two or more colors from one Light Emitting Diode, since the three or more electrode sections were needed, electrode area had to be made still smaller, and the connection with the electrode and lead member by the pewter or the conductive paste was impossible. Moreover, the light-emitting-device chip used for Light Emitting Diode by which the conventional proposal is made was using the transparent insulating substrate, and since there was the absorption of light by the substrate for the structure which takes out the light which emitted light through a substrate, there was also a trouble that luminous efficiency fell.

[0004] this invention tends to solve the aforementioned trouble and tends to offer Light Emitting Diode with a good luminescence property with sufficient reappearance simply.

[0005]

[Means for Solving the Problem] This invention persons can obtain now Light Emitting Diode which has a good property with sufficient reappearance by using the wire-bonding method, in case all the electrodes and each lead member of the element chip using the insulating substrate are connected, as a result of repeating research wholeheartedly, in order to solve the aforementioned trouble.

[0006] That is, this invention offers the light emitting diode characterized by the structure where all connections between an electrode and a lead member are wires in the element chip of the planar structure which has an electrode for having at least one luminous layer which consists of two or more sorts of combination chosen from the n-type-semiconductor layer, p type, and the i-type-semiconductor layer on the insulating substrate, and impressing voltage to the predetermined part of a semiconductor layer at a luminous layer.

[0007] If the front face is flat as an insulating substrate in this invention, it is good, and transparency is sufficient, and it is good even when it is opaque. As a thing typical as an insulating substrate, there are sapphire (aluminum 2O3), quartz (SiO2), magnesium-oxide (MgO), strontium-titanate (SrTiO3), calcium-fluoride (CaF2), and magnesium fluoride (MgF2), titanium oxide (TiO2), etc. however, it is good to use **'s whose lattice constant of the semiconductor thin film directly formed on a substrate suited to the lattice constant of this insulating substrate as much as possible. As for the grid mismatching with the semiconductor thin film directly formed on this insulating substrate and a substrate, it is good that considering as 10% or less considers as 5% or less desirable still more preferably. For this reason, it is also desirable to use that in which only the predetermined angle turned off this transparent insulation substrate. For example, in GaN, it becomes what has desirable using the substrate which turned off the Rth page of 9.2 degrees of sapphire. Moreover, when the grid mismatching of an insulating substrate and a semiconductor thin film is very large, you may prepare a buffer layer between this insulating substrate and a semiconductor thin film. As a buffer layer, the amorphous-like matter, for example, AlN, GaN, Si, SiC, etc., can prepare AlN, ZnO, SiC, etc. as single crystal matter.

[0008] As a method of forming a luminous layer on an insulating substrate in

this invention, semiconductor growth equipments, such as the MBE (Molecular Beam Epitaxy) method, the CBE (Chemical Beam Epitaxy) method, the MOMBE (Metal Organic MBE) method, the CVD (Chemical Vapour Deposition) method, and the MOCVD (Metal Organic CVD) method, can be used. A luminous layer is formed on an insulating substrate by the above-mentioned thin film production method. This luminous layer may be any of MIS structure, the single hetero structure of having pn junction and double hetero structure, quantum well structure, or a superstructure.

[0009] The luminous layer in this invention is a luminous layer which consists of two or more sorts of combination chosen from the n-type-semiconductor layer, p type, and the i-type-semiconductor layer. Moreover, although either a III-V group compound semiconductor or an II-VI group compound semiconductor is OK as the semiconductor which forms these luminous layers, the GaN system semiconductor which is a III-V group compound semiconductor is [that growth of a crystalline good thin film is possible, and] especially desirable to the sapphire which is an insulating substrate, CaF₂, MgO, etc.

[0010] The light-emitting-device chip in this invention needs to form the electrode of a positive/negative couple in the same flat surface by the side of a luminous layer, in order to use an insulating substrate, and it must etch a luminous layer. As the etching method performed to the well of this light-emitting-device chip production, you may use whichever of the wet etching method and the dry etching method according to the kind of luminous layer. Heat-treating after etching is also desirable, by performing this heat treatment, membranous degradation received by etching can be recovered, an interfacial resistance can be lowered, and current required for luminescence can be acquired by the low battery. What is necessary is just the furnace which can control the atmosphere of a tubular furnace, a lamp annealing furnace, etc. as equipment which heat-treats.

[0011] As the electrode formation method of the light-emitting-device chip in this invention, the MBE method, a vacuum deposition method, an electron-beam-evaporation method, a spatter, etc. occur. That from which ohmic contact is obtained by a n-type semiconductor, p type, or each i type semiconductor as an electrode material may be desirable, and a metal simple substance is sufficient as it, and it may use what mixed and alloyed two or more sorts of metals. The conditions for obtaining this ohmic contact have the good metal which has a work function smaller than the work function of a semiconductor as an electrode by the side of a n-type semiconductor, and it is good to use the metal which has a bigger work function as an electrode by the side of a p type semiconductor than the work function of a semiconductor. For example, in GaN which is a III-V group compound semiconductor, it is good for an n type GaN layer to use aluminum, In, Ti, Pb, Sb, Nb, Zr, Mn, etc. for an electrode, and good ohmic contact is obtained by i type or the p type GaN layer by using Au, Pt, germanium, As, Ir, Re, Rh, Pd, nickel, W, etc. for an electrode. Moreover, in order to raise an adhesive property, and to improve the thermal resistance of the polar zone, it is [be / in case / an element chip is pasted up on a lead member after this ohmic electrode formation,] also desirable to carry out the laminating of the metals, such as nickel, Ti, Au, and W, on an ohmic electrode.

[0012] It is also desirable to heat-treat below by the decomposition temperature of a semiconductor in the gas stream which contains the composition element of the inside of inert gas styles, such as Ar, N₂, and helium, or this semiconductor after electrode formation, this is enabled to lower the interfacial resistance of an electrode and a semiconductor, and it can obtain good diode characteristics. As for Light Emitting Diode in this invention, it is desirable to devise an electrode configuration in order to take the structure which takes out light from an electrode side. In order to take out the light which emitted light from an electrode side, it is that wrap electrode area makes preferably the front face of this p type or a i-type-semiconductor layer 30% or less still more preferably 40% or less 50% or less. Therefore, although an electrode needs to

form a pattern on the front face of p type or a i-type-semiconductor layer, and it can consider as the letter of a network shown in drawing 4 as an example of a pattern, the shape of CUSH which are shown in drawing 5, and the shape of MIANDA which are shown in drawing 6, and there are combination of these patterns, the shape of a whirl and an island, etc. further, it is not limited to especially these. If the width of face of an electrode and an inter-electrode distance narrow width of face of an electrode and inter-electrode distance is made small that what is necessary is just to change with the electric resistance of p type or a i-type-semiconductor layer, or the size of voltage to impress, its ejection efficiency of light will improve. While impressing voltage to the front face of p type or a i-type-semiconductor layer uniformly by making width of face of an electrode into a submicron grade, and making inter-electrode into the interval about submicron one, ejection efficiency of light can also be enlarged.

[0013] Moreover, in this invention, it will also become desirable to prepare at least a kind of metallic reflective layer as shown on the field in which the luminous layer on a substrate is not formed at drawing 11. It is enabled for this metal layer to reflect the light which emits light in the luminous layer which comes to combine a n-type-semiconductor layer and p type, or a i-type-semiconductor layer, and comes out through a substrate, and to take it out from an electrode side. Thereby, the ejection efficiency of the light of a light emitting device can be raised. As a material used as a metallic reflective layer, there are metalized simple substances or those alloys, such as aluminum, In, Cu, Ag, Pt, Ir, Pd, Rh, W, Mo, Ti, and nickel. A metallic reflective layer becomes what has at least a monostromatic desirable [also considering as the structure which carried out the laminating of the metal of high-melting points, such as nickel, W, and Mo, in order to make the pewter-proof nature when mounting in a leadframe, and thermal resistance and bonding-proof nature improve] although it is good.

[0014] The configuration of the leadframe in this invention is [that what is necessary is just the structure where other lead members are connectable with each electrode for impressing voltage to the connection for fixing an element chip to a lead member, and each part of an element chip with a wire, respectively] changeable with the electrode configuration of a light-emitting-device chip. Since luminescence is condensed effectively, as for a leadframe, it is desirable to establish a mirror side.

[0015] What is generally used for the lead member as a material of the adhesion at the time of performing die bonding in the light-emitting-device chip in this invention can be used. For example, Bi little to Au-Si, an Pb-Sn alloy system pewter, and this pewter, To what added metals, such as Sb, Ag, Cd, Zn, and In, and Bi, Na, To what added and alloyed Tl, Cd, Sn, Pb, etc., and In, Zn, Cd, There is a conductive paste containing metals, such as what added and alloyed Sn, Bi, etc., a thing which added and alloyed Ag, Zn, Sn, In, etc. to Ga, and Au, aluminum, In, Ag, Ag, Au, Cu, etc. As a method of pasting up an element chip and a lead member, there is a method using conventional die bonding equipment. namely, a glue line -- this polar zone of an element chip, or a lead -- it pastes up by heating a lead member beyond the melting point of the charge of a binder, sticking this polar zone and this lead member, after forming in the adhesion side of the element chip of a member with a vacuum deposition, the applying method, or plating

[0016] Moreover, in case the electrode section and the lead member of a light-emitting-device chip in this invention are wired, it is the feature to use the wire bonder method. after fixing an element chip to a lead member by the die bonding method -- wire-bonding equipment -- setting -- heating -- and -- or the electrode section and a lead member are connected by impressing an ultrasonic wave As a material of a wire used at this time, there are alloys, such as metals, such as Au, Ag, Cu, and aluminum, Au-Si, aluminum-Si, aluminum-Mg, aluminum-Si-Mg, and aluminum-nickel, and which material is used should just choose in consideration of the material of the electrode section of a

light-emitting-device chip, or the workability of wirebonding. Especially, I hear that workability is good and it is desirable. [of Au or aluminum-Si] The size of a wire is usually 20-300micrometerphi that what is necessary is just to choose in consideration of the workability of size **** wirebonding of the electrode section of a light-emitting-device chip. Moreover, in order to prevent oxidization of a wire, it is also a desirable method to perform wirebonding in inert gas.

[0017] It is desirable that the light transmittance in the luminescence wavelength range of a light-emitting-device chip uses 80% or more of translucency material as a closure material in this invention. As this translucency material, an methacrylic system resin, an epoxy system resin, a polycarbonate system resin, a polystyrene system resin, and POREORE fin system resin **** can use a kind, even if there are few low melting glasses. as the closure method -- the metal mold of for example, a request configuration -- the raw material or heating melting object of such translucency material -- a notes form -- carrying out -- metal mold -- the method of solidifying inside can be used As the method of this solidification, cooling solidification, a chemical reaction, etc. can be mentioned with the polymerization solidification by the heat or light of a monomer or oligomer, and a heating melting object. If there is need in this translucency material, it is also possible to add the lubricant for the antioxidant for stabilization of the coloring matter for color tone adjustment or a visibility amendment, a pigment, a fluorescent substance, etc. of a resin, a stabilizer, and a fabricating operation and lubricant.

[0018] Although the example of Light Emitting Diode produced using the all directions method explained above is shown in drawing 3 , it is not limited to this. The element chip 24 is an element chip of the planar structure which has an electrode for having at least one luminous layer which consists of two or more sorts of combination chosen from the n-type-semiconductor layer, p type, and the i type semiconductor on the insulating substrate, and impressing voltage to the predetermined part of each semiconductor layer at a luminous layer. the substrate side of this element chip, or a lead -- the lead after depositing a pewter by the vacuum deposition to the adhesion side of a member 22 -- the element chip 24 is put on the adhesion side of a member 22, and it heats beyond the melting point of a pewter and pastes up Then, each electrode and each lead member are connected by the gold streak using the wirebonding method. Then, it closes by translucency material and Light Emitting Diode25 is produced.

[0019] It is aluminum 203 as an insulating substrate as the following and an example. Although how to use it, form a GaN thin film using the MBE method, and produce Light Emitting Diode is explained, it is not limited to especially this. The gas source MBE equipment equipped with the crucibles 2, 3, and 4 for evaporation (KUNUDOSEN SERU), the gas cell 7, and the substrate heating electrode holder 5 in the vacuum housing 1 as shown in drawing 1 as equipment was used.

[0020] Ga metal was put into the crucible 2 for evaporation, and it heated to the temperature set to 1013-1019-/cm² and sec in a substrate side. It was made to spray ammonia on introduction of ammonia directly from the inside of a gas cell 7 at a substrate 6 using the gas introduction pipe 8. The amount of introduction of ammonia was supplied so that it might be set to 1016-1020-/cm² and sec in a substrate front face. In, aluminum, etc. are put into the crucible 3 for evaporation, and membranes are formed by controlling temperature and time so that it may become the semiconductor which has the compound semiconductor and the predetermined carrier density of predetermined composition. Mg, Zn, Be, Sb, Si, germanium, C, Sn, Hg, As, P, etc. are put into the crucible 4 for evaporation, it dopes by controlling temperature and supply time so that it may become the predetermined amount of supply, and n type and i type, or a p type semiconductor layer is formed.

[0021] The Rth page of sapphire was used for the substrate 6, and it heated at 200-900 degrees C. The thing of 0.8 or less degrees has [the Rth page substrate of sapphire] a desirable OFF angle. First, after heating a substrate 6 at 750

degrees C within a vacuum housing 1, each crucible is set as predetermined growth temperature, the crucible 3 for evaporation is opened first, and an n type GaN thin film with a thickness of 0.05-2 micrometers is produced by the growth rate of 0.1-30A / sec. Furthermore, after that, the shutter of the crucible 4 for evaporation which charged Zn is opened, i type or a p type GaN thin film is formed by the thickness of 0.01-1 micrometer by the growth rate of 0.1-30A / sec, and a luminous layer is formed. At the time of this membrane formation, a gas cell is always heated, and ammonia is supplied to a substrate front face.

[0022] The process which produces Light Emitting Diode using the GaN thin film which has the luminous layer which formed membranes by the above methods is explained according to drawing 2 (h) from drawing 2 (a). A vacuum deposition method is used and it is aluminum 203. The vacuum evaporationo of the metallic-reflection film 17 is carried out to a side (a). A resist is applied to a GaN thin film front face. As for the thickness of a resist, it is desirable to be referred to as 0.1-3 micrometers that what is necessary is just to change with the thickness of a GaN thin film to *****. The conditions of a spin coater are 2500rpm and 30sec. A prebake is carried out for 30 minutes within the clean oven heated by 90 degrees C after the application (b). Then, UV exposure and development were performed using the mask for element pattern formation (c). The GaN thin film 14 of i layers or p layers is removed by the ion milling method, using Ar as gas (d). A resist is removed after an ion milling end using an acetone.

[0023] In addition, it can decide on time to perform ion milling in each process by the thickness which etches. The sample was set after the above process and in the tubular furnace, and it heat-treated for 30 minutes at 500 degrees C by making ammonia into atmosphere. After having applied the resist again, having performed the prebake after heat treatment, and performing UV exposure and development using the mask for n layer electrode formation continuously, the vacuum evaporationo of the aluminum was carried out to the thickness of 3000A as an electrode of the n type GaN layer 15 by (e) and the vacuum deposition method, and the electrode pattern 19 was formed by the lift off (f). Subsequently, after having applied the resist again, performing the prebake and performing UV exposure and development using the mask for i layer electrode formation, the vacuum evaporationo of the Au was carried out to the thickness of 3000A as an electrode of p type or the i type GaN layer 14 by (g) and the vacuum deposition method, and the electrode pattern 20 was formed by the lift off (h). Then, 300 degrees C and heat-treatment of 1 hour were performed in Ar style.

[0024] the metallic-reflection film of the light-emitting-device chip produced as mentioned above -- a pewter -- a lead -- a member 22 -- pasting up -- the electrode of an n type GaN layer and an i type GaN layer -- wire bonder equipment -- using -- 30micrometerphiAu lines 23 -- respectively -- a lead -- a member 21 and a lead -- bonding was carried out to the member 22 Then, 5mmphiLight Emitting Diodes25 as perform molding by the transparent epoxy resin and show a light-emitting-device chip to drawing 3 were produced.

[0025]

[Example] Hereafter, an example explains to a detail further.

[0026]

[Example 1] aluminum2 O3 R page is used as an insulating substrate, a GaN thin film is formed by the MBE method, and the example which produced Light Emitting Diode using the element chip which has MIANDA-like electrode structure is explained. The MBE equipment equipped with the crucibles 2 and 4 for evaporation, the gas cell 7 and the substrate heating electrode holder 5, and the gas introduction pipe 8 for supplying gas to a gas cell 7 further in the vacuum housing 1 as shown in drawing 1 was used.

[0027] Ga metal was put into the crucible 2 for evaporation, and it heated at

1050 degrees C. Ammonia was used as gas and the gas cell 7 was supplied at the rate of 5 cc/min through the gas introduction pipe 8. Ammonia gas was made into structure which is directly supplied to a substrate 6. As a substrate 6, an OFF angle uses the Rth page of the sapphire which is 0.5 degrees. The pressure in a vacuum housing was 2×10^{-6} Torr at the time of membrane formation.

[0028] First, it heats for 30 minutes at 900 degrees C, and membranes are formed by subsequently to the temperature of 750 degrees C holding a substrate 6. Membrane formation is performed by opening the shutter of the crucible of Ga, supplying ammonia from the gas cell 7 heated at 300 degrees C, and it is 0.5 micrometers of thickness at 1.5A / membrane formation speed of sec. The n type GaN thin film was produced. The shutter of the crucible 4 for evaporation which furthermore charged Mg and was kept at 300 degrees C was opened, the GaN thin film of Mg dope was formed by the thickness of 0.05 micrometers of thickness at 1.5A / membrane formation speed of sec, and the luminous layer was formed. Crystallinity and flat nature were good at the shape of a streak, and when the RHEED pattern of this produced thin film measured resistance, it had resistance of 10 M omega or more, and was in the insulating state.

[0029] The vacuum deposition method was used for the opposite side of the substrate side in which the luminous layer is formed, the vacuum evaporation of the aluminum was carried out to it by the thickness of 3000A in the vacuum of 2×10^{-6} Torr, and the reflective film was formed in it. Then, on the luminous layer, the spin coater was used, the resist was applied on condition that 2500rpm and 30sec, and the prebake was carried out for 30 minutes in 90-degree C clean oven. After BEKU, using the mask for element pattern formation, UV exposure was carried out and negatives were developed. Then, ion milling was performed for 15 minutes by Ar of the conditions of acceleration voltage 500V and pressure 2×10^{-4} Torr, and element pattern formation was performed. Then, the resist was removed using the acetone. Next, the resist was again applied on condition that 2500rpm and 30sec using the spin coater, and the prebake was carried out for 30 minutes in 90-degree C clean oven. After BEKU, using the mask for i layer removal, UV exposure was carried out and negatives were developed. Then, ion milling was performed for 1 minute in Ar atmosphere of the conditions of acceleration voltage 500V and pressure 2×10^{-4} Torr, and i unnecessary layers were removed. Then, the acetone removed the resist. Subsequently, it set to the tubular furnace and 500 degrees C and heat treatment for 30 minutes were performed in the ammonia gas stream of 10 cc/min. Furthermore, the resist was applied on condition that 2500rpm and 30sec using the spin coater, and the prebake was carried out for 30 minutes in 90-degree C clean oven. After BEKU, using the mask for electrode formation of an n type GaN layer, UV exposure was carried out and negatives were developed. Then, the vacuum deposition machine was equipped and vacuum deposition of the aluminum metal was carried out by the thickness of 0.2 micrometers in the vacuum of 2×10^{-6} Torr. Then, the lift off was carried out with the acetone and the electrode pattern was formed. Subsequently, using the mask for electrode formation of an i type GaN layer, UV exposure was carried out and negatives were developed. Then, the vacuum deposition machine was equipped and vacuum deposition of the Au metal was carried out by the thickness of 0.2 micrometers in the vacuum of 2×10^{-6} Torr. Then, the lift off was carried out with the acetone and the electrode pattern was formed. Heat-treatment was performed for this produced light emitting device at 300 degrees C in Ar style for 1 hour, and the element chip which has MIANDA-like electrode structure was completed. The side elevation and plan of an element chip which were produced were shown in drawing 7 (a) and (b).

[0030] Cutting of each chip was performed using the dicing saw. The one-element chip was set to 0.5mmx0.5mm. One chip of these was taken out and die bonding of the reflective film side was carried out to the lead member with Ag paste. Furthermore, an n type GaN layer electrode, an i type GaN layer electrode, and each lead member were connected by 30micrometerphiAu lines using wire-bonding

equipment. Light Emitting Diode as closed the light emitting device produced by the above-mentioned method by the transparent epoxy resin and shown in drawing 8 was produced.

[0031] When 100 Light Emitting Diodes were produced by the same method, luminescence was checked by 99 Light Emitting Diodes. When the luminescence intensity of this Light Emitting Diode is measured, it is 60mcd(s) in 8V and 20mA, and blue luminescence was observed.

[0032]

[The example 1 of comparison] It is aluminum 203 by the same method as an example 1. Element-ization was performed using the GaN thin film which has the luminous layer which formed membranes on the substrate. Element production process was also performed by the same method as an example 1, and with Ag paste, after the two electrodes of an n type GaN layer and an i type GaN layer performed die bonding to the lead member, they were closed by the transparent epoxy resin and produced Light Emitting Diode. When 100 Light Emitting Diodes were produced by the same method, the electrode of positive/negative was connected with Ag paste and what emits light only by nine Light Emitting Diodes was not obtained.

[0033]

[Example 2] aluminum2 O3 R page is used as an insulating substrate, and the example which formed the Gai-x Inx N thin film by the MBE method, and produced Light Emitting Diode of 2 color luminescence is explained. The MBE equipment equipped with the crucibles 2, 3, and 4 for evaporation, the gas cell 7 and the substrate heating electrode holder 5, and the gas introduction pipe 8 for supplying gas to a gas cell 7 further in the vacuum housing 1 as shown in drawing 2 was used.

[0034] Ga metal was put into the crucible 2 for evaporation, and it heated at 1020 degrees C, and In metal was put into the crucible 3 for vacuum evaporation, and it heated at 1000 degrees C. Ammonia was used as gas and the gas cell 7 was supplied at the rate of 5 cc/min through the gas introduction pipe 8. Ammonia gas was made into structure which is directly supplied to a substrate 6. As a substrate 6, an OFF angle uses the Rth page of the sapphire which is 0.5 degrees.

[0035] The pressure in a vacuum housing was 2×10^{-6} Torr at the time of membrane formation. First, it heats for 30 minutes at 900 degrees C, and membranes are formed by subsequently to the temperature of 700 degrees C holding a substrate 6. Membrane formation is performed by opening the shutter of the crucible of Ga and In, supplying ammonia from the gas cell 7 heated at 300 degrees C, and it is 0.5 micrometers of thickness at 1.5A / membrane formation speed of sec. The n type Ga0.8 In0.2 N thin film was produced. The i type Ga0.8 In0.2 N thin film which opened the shutter of the crucible 4 for evaporation which furthermore charged Mg and was kept at 300 degrees C, and doped Mg was formed by the thickness of 0.05 micrometers of thickness at 1.5A / membrane formation speed of sec, and the 1st luminous layer was formed. Next, after raising substrate temperature to 750 degrees C and stabilizing temperature for 30 minutes, open the shutter of the crucible of Ga and the n type GaN thin film of 0.5 micrometers of thickness is grown up by the growth rate of 1.5A / sec. The i type GaN thin film which furthermore opened the shutter of the vacuum evaporationo crucibles 2 and 4 on it, and doped Mg was formed by the thickness of 0.05 micrometers of thickness by the growth rate of 1.5A / sec, and the 2nd luminous layer was formed.

[0036] The vacuum deposition method was used for the opposite side of the substrate side in which the luminous layer is formed, the vacuum evaporationo of the aluminum was carried out to it by the thickness of 3000A in the vacuum of 2×10^{-6} Torr, and the reflective film was formed in it. Then, on the luminous layer, the spin coater was used, the resist was applied on condition that 2500rpm and 30sec, and the prebake was carried out for 30 minutes in 90-degree C clean oven. After BEKU, using the mask for element pattern formation, UV exposure was carried out and negatives were developed. Then, ion milling was performed for 25

minutes by Ar of the conditions of acceleration voltage 500V and pressure 2×10^{-4} Torr, and element pattern formation was performed. Then, the resist was removed using the acetone. Next, the resist was again applied on condition that 2500rpm and 30sec using the spin coater, and the prebake was carried out for 30 minutes in 90-degree C clean oven. After BEKU, using the photo mask, UV exposure was carried out and negatives were developed. Then, ion milling was performed for 15 minutes in Ar atmosphere of the conditions of acceleration voltage 500V and pressure 2×10^{-4} Torr, and the unnecessary i type GaN layer, the n type GaN layer, and the i mold Ga0.8 In0.2 N layer were removed. Next, the resist was again applied on condition that 2500rpm and 30sec using the spin coater, and the prebake was carried out for 30 minutes in 90-degree C clean oven. After BEKU, using the photo mask, UV exposure was carried out and negatives were developed. Subsequently, ion milling was performed for 13 minutes in Ar atmosphere of the conditions of acceleration voltage 500V and pressure 2×10^{-4} Torr, and the unnecessary i type GaN layer and the n type GaN layer were removed. The resist was applied on condition that 2500rpm and 30sec using the spin coater further again, and the prebake was carried out for 30 minutes in 90-degree C clean oven. After BEKU, using the photo mask, UV exposure was carried out and negatives were developed. Then, the unnecessary i type GaN layer was removed using ion milling. Then, the acetone removed the resist. Subsequently, it set to the tubular furnace and 500 degrees C and heat treatment for 30 minutes were performed in the ammonia gas stream of 10 cc/min. Furthermore, the resist was applied on condition that 2500rpm and 30sec using the spin coater, and the prebake was carried out for 30 minutes in 90-degree C clean oven. After BEKU, using the mask for electrode formation of an n type GaN layer and n mold Ga0.8 In0.2 N layer, UV exposure was carried out and negatives were developed. Then, the vacuum deposition machine was equipped and vacuum deposition of the aluminum metal was carried out by the thickness of 0.2 micrometers in the vacuum of 2×10^{-6} Torr. Then, the lift off was carried out with the acetone and the electrode pattern was formed. Subsequently, using the mask for electrode formation of an i type GaN layer and i mold Ga0.8 In0.2 N layer, UV exposure was carried out and negatives were developed. Then, the vacuum deposition machine was equipped and vacuum deposition of the Au metal was carried out by the thickness of 0.2 micrometers in the vacuum of 2×10^{-6} Torr. Then, the lift off was carried out with the acetone and the electrode pattern was formed. Heat-treatment was performed for this produced light emitting device at 300 degrees C in Ar style for 1 hour, and the structure of an element chip was completed. The side elevation and plan of an element chip which were produced are shown in drawing 9 (a) and (b).

[0037] Cutting of each chip was performed using the dicing saw. The one-element chip was set to 1mmx1mm. One chip of these was taken out and die bonding of the reflective film side was carried out to the lead member with the Pb-Sn pewter. The n type GaN layer and the n mold Ga0.8 In0.2 N layer electrode were connected by 30micrometerphiAu lines using wire-bonding equipment after that. Furthermore, the i type GaN layer electrode, a lead member and an i type Ga0.8 In0.2 N layer electrode, and the lead member were connected by 30micrometerphiAu lines using wire-bonding equipment. The light emitting device produced by the above-mentioned method was closed by the transparent epoxy resin, and Light Emitting Diode as shown in drawing 10 was produced.

[0038] When 100 Light Emitting Diodes were produced by the same method, luminescence was checked by 95 Light Emitting Diodes. the place which measured the luminescence intensity of this Light Emitting Diode -- a lead -- a member 66 and a lead -- a member 67 -- 10V and luminescence with blue 40mcd(s) at 18mA -- a lead -- a member 66 and a lead -- in the member 68, 8V and luminescence with green 60mcd(s) at 20mA were observed

[0039]

[Effect of the Invention] this invention is connecting respectively all the electrodes formed in the same flat surface to the lead member divided into the same number as this number of electrodes with a wire by the wire-bonding method

in the planar type element chip structure the luminous layer's having been formed on the insulating substrate, and it becomes possible to supply Light Emitting Diode of the stable performance.

TECHNICAL FIELD

[Industrial Application] this invention relates to the light emitting diode which mounted the light-emitting-device chip which used the insulating substrate in the leadframe.

PRIOR ART

[Description of the Prior Art] Since the element chip conventionally mounted in the light emitting diode (Light Emitting Diode) put in practical use used conductive substrates, such as GaAs and InP, the polar zone of positive/negative was formed in the table and the reverse side of an element chip. The cross section of Light Emitting Diode which mounted the element chip in the conventional leadframe and was closed by the resin is shown in drawing 12 . the case where this element chip 24 is pasted up on a leadframe 49 since the element chip produced using the conductive substrate has taken the structure of having an electrode on a table and the reverse side as mentioned above -- one of the two's electrode -- the mirror section 50 of a leadframe -- a pewter or a conductive paste -- pasting up -- already -- one of the two's electrode -- the wire-bonding method -- a lead -- structure which is connected to a member 48 was taken this lead -- after mounting an element chip in members 47 and 48, it closed by the epoxy resin etc. and Light Emitting Diode25 was formed In recent years, Light Emitting Diode by the element chip of the flip chip method which used the transparent insulation substrate is proposed. (JP,4-10670,A) structure as shown in drawing 13 as a Light Emitting Diode produced using the light-emitting-device chip in which the luminous layer was formed on this transparent insulation substrate -- it is -- the electrodes 19 and 20 of the element chip 24 -- the electrode of positive/negative -- a luminous layer side -- being located -- a lead -- connection with members 51 and 52 was made with a pewter or a conductive paste

EFFECT OF THE INVENTION

[Effect of the Invention] this invention is connecting respectively all the electrodes formed in the same flat surface to the lead member divided into the same number as this number of electrodes with a wire by the wire-bonding method in the planar type element chip structure the luminous layer's having been formed on the insulating substrate, and it becomes possible to supply Light Emitting Diode of the stable performance.

TECHNICAL PROBLEM

[Problem(s) to be Solved by the Invention] Since current can be passed to a substrate when a conductive substrate is used for a light-emitting-device chip, as mentioned above, the electrode of positive/negative can be formed in a substrate side at one one and luminous layer side. Carrying out die bonding of the electrode by the side of a substrate to the lead member, when connecting with

a leadframe, the electrode by the side of a luminous layer was producing Light Emitting Diode by the method of carrying out wire bonding to other lead members. when a transparent insulation substrate is used for an element chip, in order [however,] to take the flip chip method which has the electrode of a positive/negative couple in a luminous layer side -- an element chip and a lead -- connection of a member cannot take the connection method mentioned above for this reason -- in order to connect to a leadframe two sorts of electrodes formed in the luminous layer side -- the lead of two -- the connection side with the element chip of a member is made flat, and the process which pastes up the electrode side of an element chip on this flat side with a pewter or a conductive paste is taken. However, by this method, in order to have to form two sorts of electrodes in the same field, in the element chip size below 1mm angle, electrode size had the problem that two sorts of electrode sections will contact in an according [if it kicks, will not become but] to pewter or conductive paste adhesion [carry out] process, with 200 micrometers or less. Moreover, the electrode area pasted up with the pewter or the conductive paste to an element chip size was not able to form a complicated electrode pattern like the shape of the shape of MIANDA used a latus sake in order to make light emit more efficiently, the letter of a network, or CUSH. Or when producing the multicolor light emitting diode which obtains luminescence of two or more colors from one Light Emitting Diode, since three or more polar zone was needed, electrode area had to be made still smaller, and the connection with the electrode and lead member by the pewter or the conductive paste was impossible. Moreover, the light-emitting-device chip used for Light Emitting Diode by which the conventional proposal is made was using the transparent insulating substrate, and since there was the absorption of light by the substrate for the structure which takes out the light which emitted light through a substrate, there was also a trouble that luminous efficiency fell.

[0004] this invention tends to solve the aforementioned trouble and tends to offer Light Emitting Diode with a good luminescence property with sufficient reappearance simply.

MEANS

[Means for Solving the Problem] This invention persons can obtain now Light Emitting Diode which has a good property with sufficient reappearance by using the wire-bonding method, in case all the electrodes and each lead member of the element chip using the insulating substrate are connected, as a result of repeating research wholeheartedly, in order to solve the aforementioned trouble.

[0006] That is, this invention offers the light emitting diode characterized by the structure where all connections between an electrode and a lead member are wires in the element chip of the planar structure which has an electrode for having at least one luminous layer which consists of two or more sorts of combination chosen from the n-type-semiconductor layer, p type, and the i-type-semiconductor layer on the insulating substrate, and impressing voltage to the predetermined part of a semiconductor layer at a luminous layer.

[0007] If the front face is flat as an insulating substrate in this invention, it is good, and transparency is sufficient, and it is good even when it is opaque. As a thing typical as an insulating substrate, there are sapphire (aluminum 203), quartz (SiO₂), magnesium-oxide (MgO), strontium-titanate (SrTiO₃), calcium-fluoride (CaF₂), and magnesium fluoride (MgF₂), titanium oxide (TiO₂), etc. however, it is good to use **'s whose lattice constant of the semiconductor thin film directly formed on a substrate suited to the lattice constant of this insulating substrate as much as possible As for the grid mismatching with the semiconductor thin film directly formed on this insulating

substrate and a substrate, it is good that considering as 10% or less considers as 5% or less desirable still more preferably. For this reason, it is also desirable to use that in which only the predetermined angle turned off this transparent insulation substrate. For example, in GaN, it becomes what has desirable using the substrate which turned off the Rth page of 9.2 degrees of sapphire. Moreover, when the grid mismatching of an insulating substrate and a semiconductor thin film is very large, you may prepare a buffer layer between this insulating substrate and a semiconductor thin film. As a buffer layer, the amorphous-like matter, for example, AlN, GaN, Si, SiC, etc., can prepare AlN, ZnO, SiC, etc. as single crystal matter.

[0008] As a method of forming a luminous layer on an insulating substrate in this invention, semiconductor growth equipments, such as the MBE (Molecular Beam Epitaxy) method, the CBE (Chemical Beam Epitaxy) method, the MOMBE (Metal Organic MBE) method, the CVD (Chemical Vapour Deposition) method, and the MOCVD (Metal Organic CVD) method, can be used. A luminous layer is formed on an insulating substrate by the above-mentioned thin film production method. This luminous layer may be any of MIS structure, the single hetero structure of having pn junction and double hetero structure, quantum well structure, or a superstructure.

[0009] The luminous layer in this invention is a luminous layer which consists of two or more sorts of combination chosen from the n-type-semiconductor layer, p type, and the i-type-semiconductor layer. Moreover, although either a III-V group compound semiconductor or an II-VI group compound semiconductor is OK as the semiconductor which forms these luminous layers, the GaN system semiconductor which is a III-V group compound semiconductor is [that growth of a crystalline good thin film is possible, and] especially desirable to the sapphire which is an insulating substrate, CaF₂, MgO, etc.

[0010] The light-emitting-device chip in this invention needs to form the electrode of a positive/negative couple in the same flat surface by the side of a luminous layer, in order to use an insulating substrate, and it must etch a luminous layer. As the etching method performed to the well of this light-emitting-device chip production, you may use whichever of the wet etching method and the dry etching method according to the kind of luminous layer. Heat-treating after etching is also desirable, by performing this heat treatment, membranous degradation received by etching can be recovered, an interfacial resistance can be lowered, and current required for luminescence can be acquired by the low battery. What is necessary is just the furnace which can control the atmosphere of a tubular furnace, a lamp annealing furnace, etc. as equipment which heat-treats.

[0011] As the electrode formation method of the light-emitting-device chip in this invention, the MBE method, a vacuum deposition method, an electron-beam-evaporation method a spatter, etc. occur. That from which ohmic contact is obtained by a n-type semiconductor, p type, or each i type semiconductor as an electrode material may be desirable, and a metal simple substance is sufficient as it, and it may use what mixed and alloyed two or more sorts of metals. The conditions for obtaining this ohmic contact have the good metal which has a work function smaller than the work function of a semiconductor as an electrode by the side of a n-type semiconductor, and it is good to use the metal which has a bigger work function as an electrode by the side of a p type semiconductor than the work function of a semiconductor. For example, in GaN which is a III-V group compound semiconductor, it is good for an n type GaN layer to use aluminum, In, Ti, Pb, Sb, Nb, Zr, Mn, etc. for an electrode, and good ohmic contact is obtained by i type or the p type GaN layer by using Au, Pt, germanium, As, Ir, Re, Rh, Pd, nickel, W, etc. for an electrode. Moreover, in order to raise an adhesive property, and to improve the thermal resistance of the polar zone, it is [be / in case / an element chip is pasted up on a lead member after this ohmic electrode formation,] also desirable to carry out the laminating of the metals, such as nickel, Ti, Au, and W, on an ohmic electrode.

[0012] It is also desirable to heat-treat below by the decomposition temperature of a semiconductor in the gas stream which contains the composition element of the inside of inert gas styles, such as Ar, N₂, and helium, or this semiconductor after electrode formation, this is enabled to lower the interfacial resistance of an electrode and a semiconductor, and it can obtain good diode characteristics. As for Light Emitting Diode in this invention, it is desirable to devise an electrode configuration in order to take the structure which takes out light from an electrode side. In order to take out the light which emitted light from an electrode side, it is that wrap electrode area makes preferably the front face of this p type or a i-type-semiconductor layer 30% or less still more preferably 40% or less 50% or less. Therefore, although an electrode needs to form a pattern on the front face of p type or a i-type-semiconductor layer, and it can consider as the letter of a network shown in drawing 4 as an example of a pattern, the shape of Cush which are shown in drawing 5, and the shape of MIANDA which are shown in drawing 6, and there are combination of these patterns, the shape of a whirl and an island, etc. further, it is not limited to especially these. If the width of face of an electrode and an inter-electrode distance narrow width of face of an electrode and inter-electrode distance is made small that what is necessary is just to change with the electric resistance of p type or a i-type-semiconductor layer, or the size of voltage to impress, its ejection efficiency of light will improve. While impressing voltage to the front face of p type or a i-type-semiconductor layer uniformly by making width of face of an electrode into a submicron grade, and making inter-electrode into the interval about submicron one, ejection efficiency of light can also be enlarged.

[0013] Moreover, in this invention, it will also become desirable to prepare at least a kind of metallic reflective layer as shown on the field in which the luminous layer on a substrate is not formed at drawing 11. It is enabled for this metal layer to reflect the light which emits light in the luminous layer which comes to combine a n-type-semiconductor layer and p type, or a i-type-semiconductor layer, and comes out through a substrate, and to take it out from an electrode side. Thereby, the ejection efficiency of the light of a light emitting device can be raised. As a material used as a metallic reflective layer, there are metalized simple substances or those alloys, such as aluminum, In, Cu, Ag, Pt, Ir, Pd, Rh, W, Mo, Ti, and nickel. A metallic reflective layer becomes what has at least a monostromatic desirable [also considering as the structure which carried out the laminating of the metal of high-melting points, such as nickel, W, and Mo, in order to make the pewter-proof nature when mounting in a leadframe, and thermal resistance and bonding-proof nature improve] although it is good.

[0014] The configuration of the leadframe in this invention is [that what is necessary is just the structure where other lead members are connectable with each electrode for impressing voltage to the connection for fixing an element chip to a lead member, and each part of an element chip with a wire, respectively] changeable with the electrode configuration of a light-emitting-device chip. Since luminescence is condensed effectively, as for a leadframe, it is desirable to establish a mirror side.

[0015] What is generally used for the lead member as a material of the adhesion at the time of performing die bonding in the light-emitting-device chip in this invention can be used. For example, Bi little to Au-Si, an Pb-Sn alloy system pewter, and this pewter, To what added metals, such as Sb, Ag, Cd, Zn, and In, and Bi, Na, To what added and alloyed Tl, Cd, Sn, Pb, etc., and In, Zn, Cd, There is a conductive paste containing metals, such as what added and alloyed Sn, Bi, etc., a thing which added and alloyed Ag, Zn, Sn, In, etc. to Ga, and Au, aluminum, In, Ag, Ag, Au, Cu, etc. As a method of pasting up an element chip and a lead member, there is a method using conventional die bonding equipment. namely, a glue line -- this polar zone of an element chip, or a lead -- it pastes up by heating a lead member beyond the melting point of the charge of a binder, sticking this polar zone and this lead member, after forming in the

adhesion side of the element chip of a member with a vacuum deposition, the applying method, or plating

[0016] Moreover, in case the electrode section and the lead member of a light-emitting-device chip in this invention are wired, it is the feature to use the wire bonder method. after fixing an element chip to a lead member by the die bonding method -- wire-bonding equipment -- setting -- heating -- and -- or the electrode section and a lead member are connected by impressing an ultrasonic wave As a material of a wire used at this time, there are alloys, such as metals, such as Au, Ag, Cu, and aluminum, Au-Si, aluminum-Si, aluminum-Mg, aluminum-Si-Mg, and aluminum-nickel, and which material is used should just choose in consideration of the material of the electrode section of a light-emitting-device chip, or the workability of wirebonding. Especially, I hear that workability is good and it is desirable. [of Au or aluminum-Si] The size of a wire is usually 20-300micrometerphi that what is necessary is just to choose in consideration of the workability of size **** wirebonding of the electrode section of a light-emitting-device chip. Moreover, in order to prevent oxidization of a wire, it is also a desirable method to perform wirebonding in inert gas.

[0017] It is desirable that the light transmittance in the luminescence wavelength range of a light-emitting-device chip uses 80% or more of translucency material as a closure material in this invention. As this translucency material, an methacrylic system resin, an epoxy system resin, a polycarbonate system resin, a polystyrene system resin, and POREORE fin system resin **** can use a kind, even if there are few low melting glasses. as the closure method -- the metal mold of for example, a request configuration -- the raw material or heating melting object of such translucency material -- a notes form -- carrying out -- metal mold -- the method of solidifying inside can be used As the method of this solidification, cooling solidification, a chemical reaction, etc. can be mentioned with the polymerization solidification by the heat or light of a monomer or oligomer, and a heating melting object. If there is need in this translucency material, it is also possible to add the lubricant for the antioxidant for stabilization of the coloring matter for color tone adjustment or a visibility amendment, a pigment, a fluorescent substance, etc. of a resin, a stabilizer, and a fabricating operation and lubricant.

[0018] Although the example of Light Emitting Diode produced using the all directions method explained above is shown in drawing 3 , it is not limited to this. The element chip 24 is an element chip of the planar structure which has an electrode for having at least one luminous layer which consists of two or more sorts of combination chosen from the n-type-semiconductor layer, p type, and the i type semiconductor on the insulating substrate, and impressing voltage to the predetermined part of each semiconductor layer at a luminous layer. the substrate side of this element chip, or a lead -- the lead after depositing a pewter by the vacuum deposition to the adhesion side of a member 22 -- the element chip 24 is put on the adhesion side of a member 22, and it heats beyond the melting point of a pewter and pastes up Then, each electrode and each lead member are connected by the gold streak using the wirebonding method. Then, it closes by translucency material and Light Emitting Diode25 is produced.

[0019] It is aluminum 203 as an insulating substrate as the following and an example. Although how to use it, form a GaN thin film using the MBE method, and produce Light Emitting Diode is explained, it is not limited to especially this. The gas source MBE equipment equipped with the crucibles 2, 3, and 4 for evaporation (KUNUDOSENTERU), the gas cell 7, and the substrate heating electrode holder 5 in the vacuum housing 1 as shown in drawing 1 as equipment was used.

[0020] Ga metal was put into the crucible 2 for evaporation, and it heated to the temperature set to 1013-1019-/cm² and sec in a substrate side. It was made to spray ammonia on introduction of ammonia directly from the inside of a gas cell 7 at a substrate 6 using the gas introduction pipe 8. The amount of introduction of ammonia was supplied so that it might be set to 1016-1020-/cm² and sec in a

substrate front face. In, aluminum, etc. are put into the crucible 3 for evaporation, and membranes are formed by controlling temperature and time so that it may become the semiconductor which has the compound semiconductor and the predetermined carrier density of predetermined composition. Mg, Zn, Be, Sb, Si, germanium, C, Sn, Hg, As, P, etc. are put into the crucible 4 for evaporation, it dopes by controlling temperature and supply time so that it may become the predetermined amount of supply, and n type and i type, or a p type semiconductor layer is formed.

[0021] The Rth page of sapphire was used for the substrate 6, and it heated at 200-900 degrees C. The thing of 0.8 or less degrees has [the Rth page substrate of sapphire] a desirable OFF angle. First, after heating a substrate 6 at 750 degrees C within a vacuum housing 1, each crucible is set as predetermined growth temperature, the crucible 3 for evaporation is opened first, and an n type GaN thin film with a thickness of 0.05-2 micrometers is produced by the growth rate of 0.1-30A / sec. Furthermore, after that, the shutter of the crucible 4 for evaporation which charged Zn is opened, i type or a p type GaN thin film is formed by the thickness of 0.01-1 micrometer by the growth rate of 0.1-30A / sec, and a luminous layer is formed. At the time of this membrane formation, a gas cell is always heated, and ammonia is supplied to a substrate front face.

[0022] The process which produces Light Emitting Diode using the GaN thin film which has the luminous layer which formed membranes by the above methods is explained according to drawing 2 (h) from drawing 2 (a). A vacuum deposition method is used and it is aluminum 203. The vacuum evaporationo of the metallic-reflection film 17 is carried out to a side (a). A resist is applied to a GaN thin film front face. As for the thickness of a resist, it is desirable to be referred to as 0.1-3 micrometers that what is necessary is just to change with the thickness of a GaN thin film to *****. The conditions of a spin coater are 2500rpm and 30sec. A prebake is carried out for 30 minutes within the clean oven heated by 90 degrees C after the application (b). Then, UV exposure and development were performed using the mask for element pattern formation (c). The GaN thin film 14 of i layers or p layers is removed by the ion milling method, using Ar as gas (d). A resist is removed after an ion milling end using an acetone.

[0023] In addition, it can decide on time to perform ion milling in each process by the thickness which etches. The sample was set after the above process and in the tubular furnace, and it heat-treated for 30 minutes at 500 degrees C by making ammonia into atmosphere. After having applied the resist again, having performed the prebake after heat treatment, and performing UV exposure and development using the mask for n layer electrode formation continuously, the vacuum evaporationo of the aluminum was carried out to the thickness of 3000A as an electrode of the n type GaN layer 15 by (e) and the vacuum deposition method, and the electrode pattern 19 was formed by the lift off (f). Subsequently, after having applied the resist again, performing the prebake and performing UV exposure and development using the mask for i layer electrode formation, the vacuum evaporationo of the Au was carried out to the thickness of 3000A as an electrode of p type or the i type GaN layer 14 by (g) and the vacuum deposition method, and the electrode pattern 20 was formed by the lift off (h). Then, 300 degrees C and heat-treatment of 1 hour were performed in Ar style.

[0024] the metallic-reflection film of the light-emitting-device chip produced as mentioned above -- a pewter -- a lead -- a member 22 -- pasting up -- the electrode of an n type GaN layer and an i type GaN layer -- wire bonder equipment -- using -- 30micrometerphiAu lines 23 -- respectively -- a lead -- a member 21 and a lead -- bonding was carried out to the member 22 Then, 5mmphiLight Emitting Diodes25 as perform molding by the transparent epoxy resin and show a light-emitting-device chip to drawing 3 were produced.

EXAMPLE

[Example] Hereafter, an example explains to a detail further.

[0026]

[Example 1] aluminum₂ O₃ R page is used as an insulating substrate, a GaN thin film is formed by the MBE method, and the example which produced Light Emitting Diode using the element chip which has MIANDA-like electrode structure is explained. The MBE equipment equipped with the crucibles 2 and 4 for evaporation, the gas cell 7 and the substrate heating electrode holder 5, and the gas introduction pipe 8 for supplying gas to a gas cell 7 further in the vacuum housing 1 as shown in drawing 1 was used.

[0027] Ga metal was put into the crucible 2 for evaporation, and it heated at 1050 degrees C. Ammonia was used as gas and the gas cell 7 was supplied at the rate of 5 cc/min through the gas introduction pipe 8. Ammonia gas was made into structure which is directly supplied to a substrate 6. As a substrate 6, an OFF angle uses the Rth page of the sapphire which is 0.5 degrees. The pressure in a vacuum housing was 2x10⁻⁶Torr at the time of membrane formation.

[0028] First, it heats for 30 minutes at 900 degrees C, and membranes are formed by subsequently to the temperature of 750 degrees C holding a substrate 6. Membrane formation is performed by opening the shutter of the crucible of Ga, supplying ammonia from the gas cell 7 heated at 300 degrees C, and it is 0.5 micrometers of thickness at 1.5A / membrane formation speed of sec. The n type GaN thin film was produced. The shutter of the crucible 4 for evaporation which furthermore charged Mg and was kept at 300 degrees C was opened, the GaN thin film of Mg dope was formed by the thickness of 0.05 micrometers of thickness at 1.5A / membrane formation speed of sec, and the luminous layer was formed. Crystallinity and flat nature were good at the shape of a streak, and when the RHEED pattern of this produced thin film measured resistance, it had resistance of 10 M omega or more, and was in the insulating state.

[0029] The vacuum deposition method was used for the opposite side of the substrate side in which the luminous layer is formed, the vacuum evaporation of the aluminum was carried out to it by the thickness of 3000A in the vacuum of 2x10⁻⁶Torr, and the reflective film was formed in it. Then, on the luminous layer, the spin coater was used, the resist was applied on condition that 2500rpm and 30sec, and the prebake was carried out for 30 minutes in 90-degree C clean oven. After BEKU, using the mask for element pattern formation, UV exposure was carried out and negatives were developed. Then, ion milling was performed for 15 minutes by Ar of the conditions of acceleration voltage 500V and pressure 2x10⁻⁴Torr, and element pattern formation was performed. Then, the resist was removed using the acetone. Next, the resist was again applied on condition that 2500rpm and 30sec using the spin coater, and the prebake was carried out for 30 minutes in 90-degree C clean oven. After BEKU, using the mask for i layer removal, UV exposure was carried out and negatives were developed. Then, ion milling was performed for 1 minute in Ar atmosphere of the conditions of acceleration voltage 500V and pressure 2x10⁻⁴Torr, and i unnecessary layers were removed. Then, the acetone removed the resist. Subsequently, it set to the tubular furnace and 500 degrees C and heat treatment for 30 minutes were performed in the ammonia gas stream of 10 cc/min. Furthermore, the resist was applied on condition that 2500rpm and 30sec using the spin coater, and the prebake was carried out for 30 minutes in 90-degree C clean oven. After BEKU, using the mask for electrode formation of an n type GaN layer, UV exposure was carried out and negatives were developed. Then, the vacuum deposition machine was equipped and vacuum deposition of the aluminum metal was carried out by the thickness of 0.2 micrometers in the vacuum of 2x10⁻⁶Torr. Then, the lift off was

carried out with the acetone and the electrode pattern was formed. Subsequently, using the mask for electrode formation of an i type GaN layer, UV exposure was carried out and negatives were developed. Then, the vacuum deposition machine was equipped and vacuum deposition of the Au metal was carried out by the thickness of 0.2 micrometers in the vacuum of 2×10^{-6} Torr. Then, the lift off was carried out with the acetone and the electrode pattern was formed. Heat-treatment was performed for this produced light emitting device at 300 degrees C in Ar style for 1 hour, and the element chip which has MIANDA-like electrode structure was completed. The side elevation and plan of an element chip which were produced were shown in drawing 7 (a) and (b).

[0030] Cutting of each chip was performed using the dicing saw. The one-element chip was set to 0.5mm x 0.5mm. One chip of these was taken out and die bonding of the reflective film side was carried out to the lead member with Ag paste. Furthermore, an n type GaN layer electrode, an i type GaN layer electrode, and each lead member were connected by 30micrometerphiAu lines using wire-bonding equipment. Light Emitting Diode as closed the light emitting device produced by the above-mentioned method by the transparent epoxy resin and shown in drawing 8 was produced.

[0031] When 100 Light Emitting Diodes were produced by the same method, luminescence was checked by 99 Light Emitting Diodes. When the luminescence intensity of this Light Emitting Diode is measured, it is 60mcd(s) in 8V and 20mA, and blue luminescence was observed.

[0032]

[The example 1 of comparison] It is aluminum 203 by the same method as an example 1. Element-ization was performed using the GaN thin film which has the luminous layer which formed membranes on the substrate. Element production process was also performed by the same method as an example 1, and with Ag paste, after the two electrodes of an n type GaN layer and an i type GaN layer performed die bonding to the lead member, they were closed by the transparent epoxy resin and produced Light Emitting Diode. When 100 Light Emitting Diodes were produced by the same method, the electrode of positive/negative was connected with Ag paste and what emits light only by nine Light Emitting Diodes was not obtained.

[0033]

[Example 2] aluminum2 O3 R page is used as an insulating substrate, and the example which formed the Ga_{1-x} In_x N thin film by the MBE method, and produced Light Emitting Diode of 2 color luminescence is explained. The MBE equipment equipped with the crucibles 2, 3, and 4 for evaporation, the gas cell 7 and the substrate heating electrode holder 5, and the gas introduction pipe 8 for supplying gas to a gas cell 7 further in the vacuum housing 1 as shown in drawing 2 was used.

[0034] Ga metal was put into the crucible 2 for evaporation, and it heated at 1020 degrees C, and In metal was put into the crucible 3 for vacuum evaporation, and it heated at 1000 degrees C. Ammonia was used as gas and the gas cell 7 was supplied at the rate of 5 cc/min through the gas introduction pipe 8. Ammonia gas was made into structure which is directly supplied to a substrate 6. As a substrate 6, an OFF angle uses the Rth page of the sapphire which is 0.5 degrees.

[0035] The pressure in a vacuum housing was 2×10^{-6} Torr at the time of membrane formation. First, it heats for 30 minutes at 900 degrees C, and membranes are formed by subsequently to the temperature of 700 degrees C holding a substrate 6. Membrane formation is performed by opening the shutter of the crucible of Ga and In, supplying ammonia from the gas cell 7 heated at 300 degrees C, and it is 0.5 micrometers of thickness at 1.5A / membrane formation speed of sec. The n type Ga0.8 In0.2 N thin film was produced. The i type Ga0.8 In0.2 N thin film which opened the shutter of the crucible 4 for evaporation which furthermore charged Mg and was kept at 300 degrees C, and doped Mg was formed by the thickness of 0.05 micrometers of thickness at 1.5A / membrane formation speed of sec, and the 1st luminous layer was formed. Next, after raising substrate

temperature to 750 degrees C and stabilizing temperature for 30 minutes, open the shutter of the crucible of Ga and the n type GaN thin film of 0.5 micrometers of thickness is grown up by the growth rate of 1.5A / sec. The i type GaN thin film which furthermore opened the shutter of the vacuum evaporationo crucibles 2 and 4 on it, and doped Mg was formed by the thickness of 0.05 micrometers of thickness by the growth rate of 1.5A / sec, and the 2nd luminous layer was formed.

[0036] The vacuum deposition method was used for the opposite side of the substrate side in which the luminous layer is formed, the vacuum evaporationo of the aluminum was carried out to it by the thickness of 3000A in the vacuum of 2×10^{-6} Torr, and the reflective film was formed in it. Then, on the luminous layer, the spin coater was used, the resist was applied on condition that 2500rpm and 30sec, and the prebake was carried out for 30 minutes in 90-degree C clean oven. After BEKU, using the mask for element pattern formation, UV exposure was carried out and negatives were developed. Then, ion milling was performed for 25 minutes by Ar of the conditions of acceleration voltage 500V and pressure 2×10^{-4} Torr, and element pattern formation was performed. Then, the resist was removed using the acetone. Next, the resist was again applied on condition that 2500rpm and 30sec using the spin coater, and the prebake was carried out for 30 minutes in 90-degree C clean oven. After BEKU, using the photo mask, UV exposure was carried out and negatives were developed. Then, ion milling was performed for 15 minutes in Ar atmosphere of the conditions of acceleration voltage 500V and pressure 2×10^{-4} Torr, and the unnecessary i type GaN layer, the n type GaN layer, and the i mold Ga0.8 In0.2 N layer were removed. Next, the resist was again applied on condition that 2500rpm and 30sec using the spin coater, and the prebake was carried out for 30 minutes in 90-degree C clean oven. After BEKU, using the photo mask, UV exposure was carried out and negatives were developed. Subsequently, ion milling was performed for 13 minutes in Ar atmosphere of the conditions of acceleration voltage 500V and pressure 2×10^{-4} Torr, and the unnecessary i type GaN layer and the n type GaN layer were removed. The resist was applied on condition that 2500rpm and 30sec using the spin coater further again, and the prebake was carried out for 30 minutes in 90-degree C clean oven. After BEKU, using the photo mask, UV exposure was carried out and negatives were developed. Then, the unnecessary i type GaN layer was removed using ion milling. Then, the acetone removed the resist. Subsequently, it set to the tubular furnace and 500 degrees C and heat treatment for 30 minutes were performed in the ammonia gas stream of 10 cc/min. Furthermore, the resist was applied on condition that 2500rpm and 30sec using the spin coater, and the prebake was carried out for 30 minutes in 90-degree C clean oven. After BEKU, using the mask for electrode formation of an n type GaN layer and n mold Ga0.8 In0.2 N layer, UV exposure was carried out and negatives were developed. Then, the vacuum deposition machine was equipped and vacuum deposition of the aluminum metal was carried out by the thickness of 0.2 micrometers in the vacuum of 2×10^{-6} Torr. Then, the lift off was carried out with the acetone and the electrode pattern was formed. Subsequently, using the mask for electrode formation of an i type GaN layer and i mold Ga0.8 In0.2 N layer, UV exposure was carried out and negatives were developed. Then, the vacuum deposition machine was equipped and vacuum deposition of the Au metal was carried out by the thickness of 0.2 micrometers in the vacuum of 2×10^{-6} Torr. Then, the lift off was carried out with the acetone and the electrode pattern was formed. Heat-treatment was performed for this produced light emitting device at 300 degrees C in Ar style for 1 hour, and the structure of an element chip was completed. The side elevation and plan of an element chip which were produced are shown in drawing 9 (a) and (b).

[0037] Cutting of each chip was performed using the dicing saw. The one-element chip was set to 1mmx1mm. One chip of these was taken out and die bonding of the reflective film side was carried out to the lead member with the Pb-Sn pewter. The n type GaN layer and the n mold Ga0.8 In0.2 N layer electrode were connected by 30micrometerphiAu lines using wire-bonding equipment after

that. Furthermore, the i type GaN layer electrode, a lead member and an i type Ga0.8 In0.2 N layer electrode, and the lead member were connected by 30micrometerphiAu lines using wire-bonding equipment. The light emitting device produced by the above-mentioned method was closed by the transparent epoxy resin, and Light Emitting Diode as shown in drawing 10 was produced.

[0038] When 100 Light Emitting Diodes were produced by the same method, luminescence was checked by 95 Light Emitting Diodes. the place which measured the luminescence intensity of this Light Emitting Diode -- a lead -- a member 66 and a lead -- a member 67 -- 10V and luminescence with blue 40mcd(s) at 18mA -- a lead -- a member 66 and a lead -- in the member 68, 8V and luminescence with green 60mcd(s) at 20mA were observed

DESCRIPTION OF DRAWINGS

[Brief Description of the Drawings]

[Drawing 1] It is the schematic diagram of the MBE equipment used for thin film production.

[Drawing 2] (a) - (h) It is the cross section having shown the production process of Light Emitting Diode.

[Drawing 3] It is the cross section of Light Emitting Diode produced by the method by this invention.

[Drawing 4] It is the plan of the light emitting device in which the letter electrode of a network was formed.

[Drawing 5] It is the plan of the light emitting device in which the Cush-like electrode was formed.

[Drawing 6] It is the plan of the light emitting device in which the MIANDA-like electrode was formed.

[Drawing 7] (a) It is the cross section of the element chip produced in the example 1.

(b) It is the plan of the element chip produced in the example 1.

[Drawing 8] It is the cross section of Light Emitting Diode produced in the example 1.

[Drawing 9] (a) It is the cross section of the element chip produced in the example 2.

(b) It is the plan of the element chip produced in the example 2.

[Drawing 10] It is the cross section of Light Emitting Diode produced in the example 2.

[Drawing 11] It is the cross section of a light emitting device which consists of structure where the metal layer was formed in the near substrate side in which a luminous layer is not formed.

[Drawing 12] It is the cross section of Light Emitting Diode produced by the conventional method.

[Drawing 13] It is the cross section of Light Emitting Diode of the flip chip method produced by the conventional method.

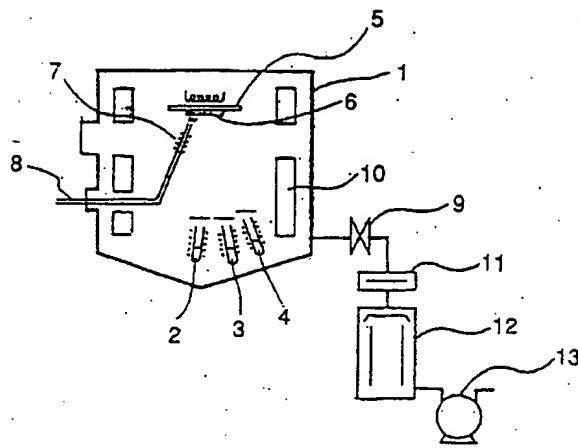
[Description of Notations]

- 1 Vacuum Housing
- 2 Crucible for Evaporation
- 3 Crucible for Evaporation
- 4 Crucible for Evaporation
- 5 Substrate Heating Electrode Holder
- 6 Substrate
- 7 Gas Cell
- 8 Gas Introduction Pipe
- 9 Flow Regulation Bulb
- 10 Cryopanel
- 11 Cold Trap
- 12 Oil Diffusion Pump

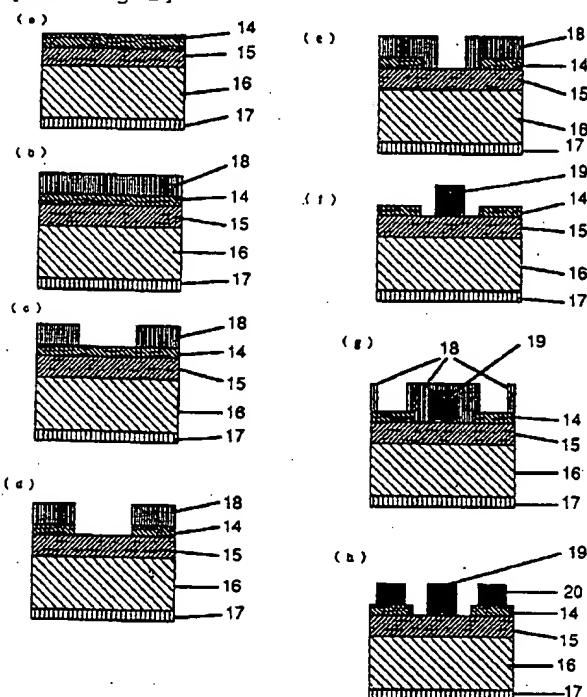
- 13 Oil Sealed Rotary Pump
- 14 P Type or I-Type-Semiconductor Layer
- 15 N-type-Semiconductor Layer
- 16 Insulating Substrate
- 17 Metallic-Reflection Film
- 18 Resist
- 19 N-type-Semiconductor Layer Electrode
- 20 P Type or I-Type-Semiconductor Layer Electrode
- 21 Lead Member (1)
- 22 Lead Member (2)
- 23 Metal Wire
- 24 Element Chip
- 25 LED
- 26 Electrode
- 27 I Type GaN Layer Electrode
- 28 N Type GaN Layer Electrode
- 29 I Type GaN Layer
- 30 N Type GaN Layer
- 31 Silicon on Sapphire
- 32 Aluminum Reflective Film
- 33 Lead Member (3)
- 34 Lead Member (4)
- 35 Au Wire
- 36 GaN Light-Emitting-Device Chip
- 37 GaNMIS Type Light Emitting Diode
- 38 I Type Ga_{0.8} In_{0.2} N Layer Electrode
- 39 N Type GaN Layer and N Type Ga_{0.8} In_{0.2} N Layer Electrode
- 40 I Mold Ga_{0.8} In_{0.2} N Layer
- 41 N Mold Ga_{0.8} In_{0.2} N Layer
- 42 Lead Member (5)
- 43 Lead Member (6)
- 44 Lead Member (7)
- 45 GaN, Ga_{0.8} In_{0.2} N Light-Emitting-Device Chip
- 46 2 Color Luminescence Light Emitting Diode
- 47 Lead Member (8)
- 48 Lead Member (9)
- 49 Leadframe
- 50 Mirror Side
- 51 Lead Member (10)
- 52 Lead Member (11)

DRAWINGS

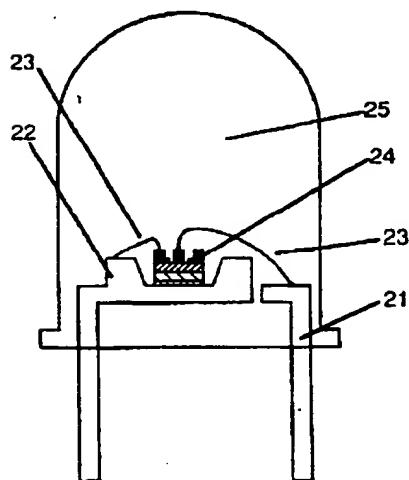
[Drawing 1]



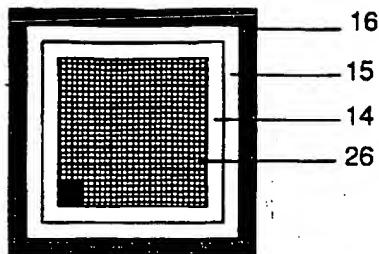
[Drawing 2]



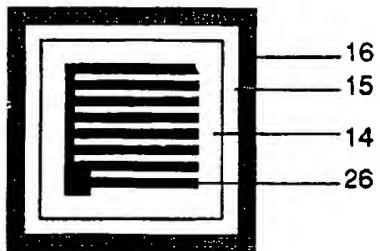
[Drawing 3]



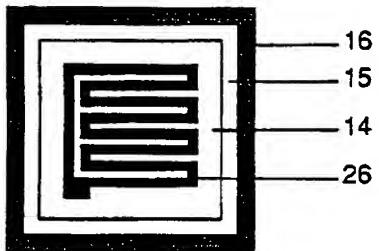
[Drawing 4]



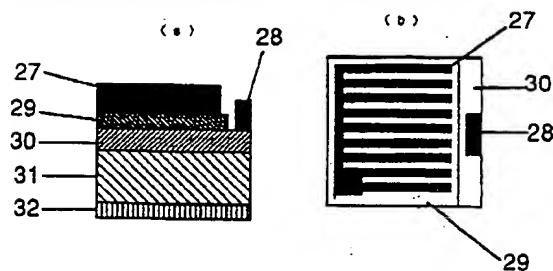
[Drawing 5]



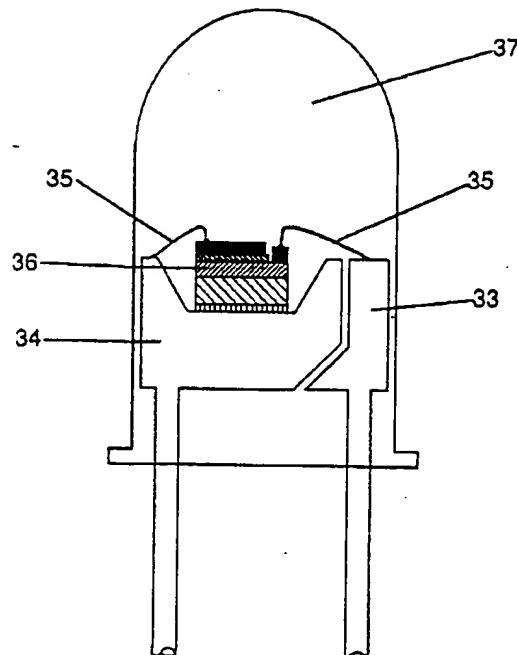
[Drawing 6]



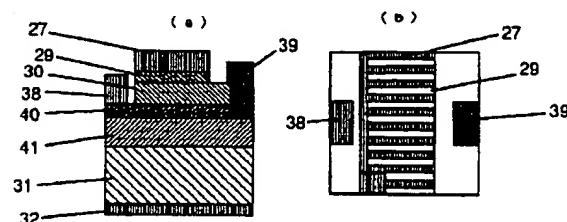
[Drawing 7]



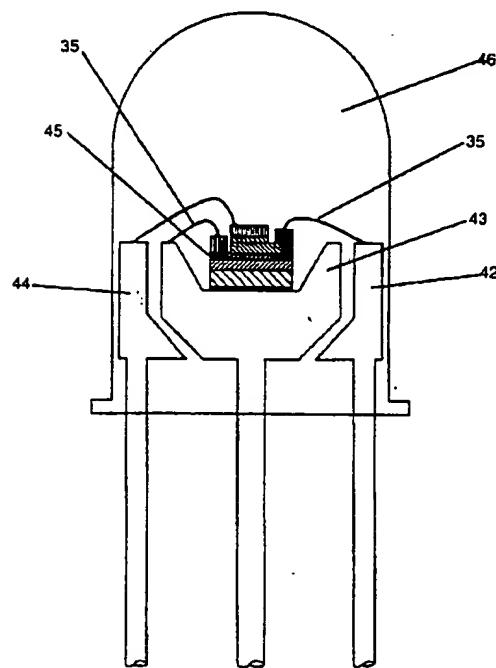
[Drawing 8]



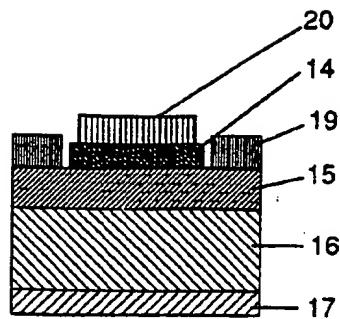
[Drawing 9]



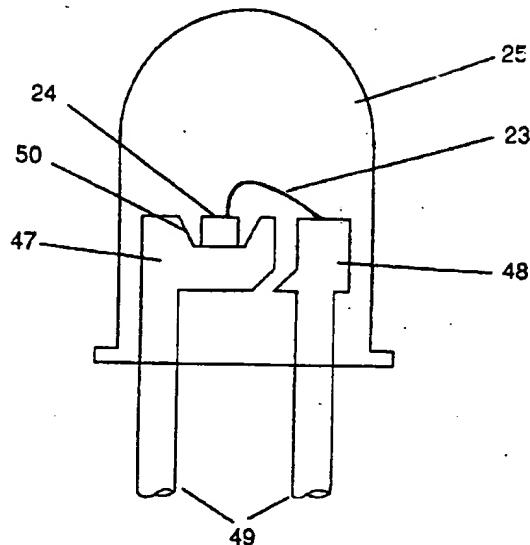
[Drawing 10]



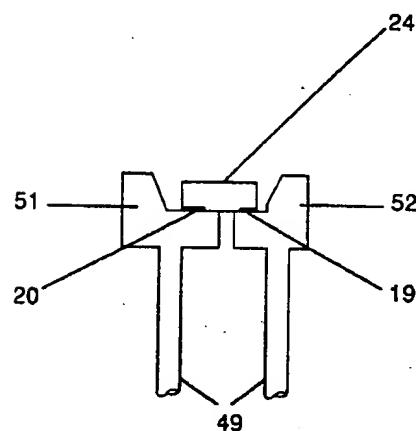
[Drawing 11]



[Drawing 12]



[Drawing 13]



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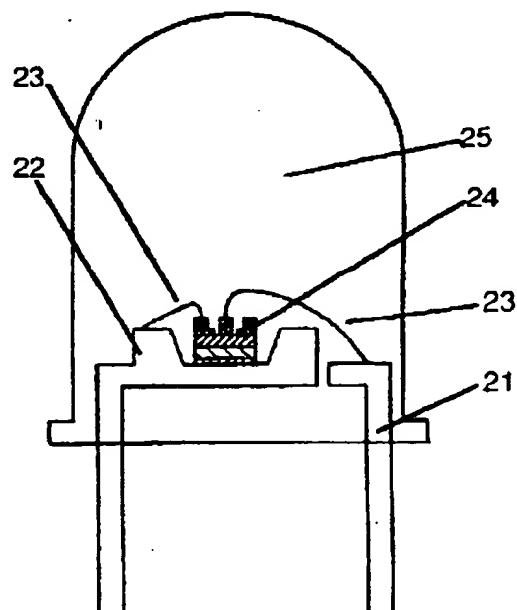
株式会社内

(54)【発明の名称】 発光ダイオード

(57)【要約】

【構成】 絶縁性基板上にn型半導体層、p型およびi型半導体層から選ばれた2種以上の組み合わせからなる発光層を少なくとも一つ有し、かつ半導体層の所定の部位に発光層に電圧を印加するための電極を有するブレーナ構造の素子チップにおいて、電極とリード部材との接続が全てワイヤーである構造を特徴とする発光ダイオード。

【効果】 電極間の接触が少なく、発光性能に優れた、品質の安定したLEDが得られる。



【特許請求の範囲】

【請求項1】 絶縁性基板上にn型半導体層、p型および1型半導体層から選ばれた2種以上の組み合わせからなる発光層を少なくとも一つ有し、かつ半導体層の所定の部位に発光層に電圧を印加するための電極を有するブレーナ構造の素子チップにおいて、電極とリード部材との接続部が全てワイヤーである構造を特徴とする発光ダイオード。

【発明の詳細な説明】

【0001】

【産業上の利用分野】 本発明は、絶縁性基板を用いた発光素子チップをリードフレームに実装した発光ダイオードに関する。

【0002】

【従来の技術】 従来、実用化されている発光ダイオード(LED)に実装されている素子チップはGaAs、InPなどの導電性基板を用いていることから正負の電極部は素子チップの表と裏に形成されていた。従来のリードフレームに素子チップを実装し樹脂で封止したLEDの断面図を図12に示す。上述したように導電性基板を用いて作製した素子チップは表と裏に電極を有する構造をとっているため、この素子チップ24をリードフレーム49に接着する場合には片方の電極をリードフレームのミラー部50にハンダあるいは導電性ペーストにより接着し、もう片方の電極はワイヤーボンディング法によってリード部材48に接続するような構造をとっていた。このリード部材47、48に素子チップを実装した後にエポキシ樹脂などで封止してLED25を形成していた。近年では、透明絶縁性基板を用いたフリップチップ方式の素子チップによるLEDが提案されている。(特開平4-10670)この透明絶縁性基板上に発光層を形成した発光素子チップを用いて作製したLEDとしては、図13に示すような構造であり、素子チップ24の電極19、20は正負の電極とも発光層側に位置し、リード部材51、52との接続は、ハンダあるいは導電性ペーストにより行われていた。

【0003】

【発明が解決しようとする課題】 上述したように発光素子チップに導電性基板を用いたときには、基板に電流を流すことができるので、正負の電極は基板側に1つ、発光層側に1つ形成することが可能である。リードフレームに接続する際には基板側の電極をリード部材にダイボンディングし、発光層側の電極は他のリード部材にワイヤーボンディングするという方法でLEDを作製していた。しかし、透明絶縁性基板を素子チップに用いた場合には、発光層側に正負一対の電極を有するフリップチップ方式をとるため、素子チップとリード部材の接続は上述した接続方法をとることができない。このため、発光層側に形成された2種の電極をリードフレームに接続するためには、2本のリード部材の素子チップとの接続面

は平坦にして、この平坦面に素子チップの電極面をハンダあるいは導電性ペーストにより接着する工程をとる。

しかしこの方法では、同一面内に2種の電極を形成しなければならないため1mm角以下の素子チップサイズでは電極サイズは200μm以下としなければならず、ハンダあるいは導電性ペーストによる接着工程において2種の電極部が接触してしまうという問題があった。また、素子チップサイズに対するハンダあるいは導電性ペーストにより接着される電極面積が広いため、より効率

10 よく発光させるために用いられるミアンダ状、ネット状あるいはクシ状のような複雑な電極パターンを形成することはできなかった。あるいは、1つのLEDから2色以上の発光を得る多色発光ダイオードを作製する場合には、3カ所以上の電極部を必要とするため電極面積はさらに小さくしなければならず、ハンダあるいは導電性ペーストによる電極とリード部材との接続は不可能であった。また、従来提案されているLEDに用いる発光素子チップは透明な絶縁性基板を使用しており、発光した光を基板を通して取り出す構造のために基板による光の吸収があるため発光効率が低下するという問題点もあった。

【0004】 本発明は、前記問題点を解決して簡単に再現よく発光特性の良好なLEDを提供しようとするものである。

【0005】

【課題を解決するための手段】 本発明者は前記問題点を解決するために鋭意研究を重ねた結果、絶縁性基板を用いた素子チップの全ての電極と各リード部材とを接続する際にワイヤーボンディング法を用いることで、再現よく良好な特性を有するLEDを得ることができるようになったものである。

【0006】 すなわち、本発明は絶縁性基板上にn型半導体層、p型および1型半導体層から選ばれた2種以上の組み合わせからなる発光層を少なくとも一つ有し、かつ半導体層の所定の部位に発光層に電圧を印加するための電極を有するブレーナ構造の素子チップにおいて、電極とリード部材との接続が全てワイヤーである構造を特徴とする発光ダイオードを提供するものである。

【0007】 本発明における絶縁性基板としては表面が40平坦であればよく、透明でもよく不透明でもよい。絶縁性基板として代表的なものとしては、サファイア(A1:O₂)、石英(SiO₂)、酸化マグネシウム(MgO)、チタン酸ストロンチウム(SrTiO₃)、フッ化カルシウム(CaF₂)、フッ化マグネシウム(MgF₂)、酸化チタン(TiO₂)などがある。しかし、基板上に直接形成する半導体薄膜の格子定数がこの絶縁性基板の格子定数に極力合ったものを用いるのがよい。この絶縁性基板と基板上に直接形成する半導体薄膜との格子不整合は10%以下とするのが好ましく、さらに好ましくは5%以下とするのがよい。このために該透

明絶縁性基板を所定の角度だけオフしたものを使用することも好ましいものである。例えばGaNの場合はサファイアR面を9.2°オフした基板を用いることが好ましいものとなる。また絶縁性基板と半導体薄膜との格子不整合が非常に大きい場合には、この絶縁性基板と半導体薄膜との間にバッファ層を設けてよい。バッファ層としてはアモルファス状の物質、例えばAlN、GaN、Si、SiCなど、あるいは単結晶物質として、例えばAlN、ZnO、SiC等を設けることができる。

【0008】本発明において絶縁性基板上に発光層を形成する方法としては、MBE (Molecular Beam Epitaxy) 法、CBE (Chemical Beam Epitaxy) 法、MOMBE (Metal Organic MBE) 法、CVD (Chemical Vapour Deposition) 法、MOCVD (Metal Organic CVD) 法等の半導体成長装置を用いることができる。上記した薄膜作製方法により絶縁性基板上に発光層を形成する。この発光層はMIS構造、pn接合を有するシングルヘテロ構造およびダブルヘテロ構造、あるいは量子井戸構造あるいは超格子構造のいずれであってもよい。

【0009】本発明における発光層とは、n型半導体層、p型およびi型半導体層から選ばれた2種以上の組み合わせからなる発光層のことである。また、これらの発光層を形成する半導体は、III-V族化合物半導体、II-VI族化合物半導体のどちらでもよいが、III-V族化合物半導体であるGaN系半導体は絶縁性基板であるサファイア、CaF₂、MgO等に結晶性の良好な薄膜の成長が可能であり特に好ましいものである。

【0010】本発明での発光素子チップは絶縁性基板を用いるために発光層側の同一平面内に正負一対の電極を形成する必要があり、発光層のエッチングを行わなければならない。この発光素子チップ作製のために行うエッチング方法としては発光層の種類により、ウェットエッチング法、ドライエッチング法のどちらを用いてもよい。エッチング後に熱処理を行うことも好ましいことであり、この熱処理を行うことによりエッチングにより受けた膜質の劣化を回復することができ、界面抵抗を下げて低電圧で発光に必要な電流を得ることができる。熱処理を行う装置としては管状炉、ランプアニール炉等の雰囲気を制御できる炉であればよい。

【0011】本発明における発光素子チップの電極形成方法としては、MBE法、真空蒸着法、電子ビーム蒸着法、スパッタ法等がある。電極材料としてはn型半導体とp型あるいはi型半導体それぞれにオーミック接触が得られるものが好ましく、金属単体でもよく、2種以上の金属を混合して合金化したものを用いてもよい。このオーミック接触を得るために条件はn型半導体側の電極としては半導体の仕事関数よりも小さな仕事関数を有す

る金属がよく、p型半導体側の電極としては半導体の仕事関数よりも大きな仕事関数を有する金属を用いるのがよい。例えば、III-V族化合物半導体であるGaNの場合には、n型GaN層にはAl、In、Ti、Pb、Sb、Nb、Zr、Mn等を電極に用いることがよく、i型あるいはp型GaN層にはAu、Pt、Ge、As、Ir、Re、Rh、Pd、Ni、W等を電極に用いることで良好なオーミック接触が得られる。また、このオーミック電極形成後に素子チップをリード部材に接着する際に、接着性を向上させるためや、電極部の耐熱性を向上するためにオーミック電極上にNi、Ti、Au、W等の金属を積層することも好ましい。

【0012】電極形成後にAr、N₂、He等の不活性ガス流中あるいは該半導体の構成元素を含むガス流中で半導体の分解温度以下で熱処理することも好ましく、これにより電極と半導体との界面抵抗を下げる事が可能になり、良好なダイオード特性を得ることができる。本発明におけるLEDは電極側から光を取り出す構造をとるため電極形状を工夫することが好ましい。発光した光を電極側から取り出すために該p型あるいはi型半導体層の表面を覆う電極面積は50%以下、好ましくは40%以下、さらに好ましくは30%以下とすることである。そのために、電極はp型あるいはi型半導体層の表面上にパターンを形成することが必要で、パターンの例としては図4に示すネット状、図5に示すクシ状、図6に示すミアンダ状とすることができるが、さらにはこれらのパターンの組合せや渦状、島状等があるが、特にこれらに限定されるものではない。電極の幅と電極間の距離はp型あるいはi型半導体層の電気抵抗や印加する電圧の大きさにより変えればよく、電極の幅を狭くして、電極間の距離を小さくすれば、光の取り出し効率が向上する。電極の幅をサブミクロン程度とし、かつ電極間もサブミクロン程度の間隔とすることによりp型あるいはi型半導体層の表面に均一に電圧を印加するとともに光の取り出し効率も大きくすることができる。

【0013】また、本発明においては、基板上の発光層が形成されていない面上に図11に示すような少なくとも一種の金属反射層を設けることも好ましいものとなる。この金属層はn型半導体層およびp型あるいはi型半導体層を組み合わせてなる発光層において発光して基板を通して出てくる光を反射して電極側から取り出すことを可能とするものである。これにより、発光素子の光の取り出し効率を高めることができる。金属反射層として使われる材料としてはAl、In、Cu、Ag、Pt、Ir、Pd、Rh、W、Mo、Ti、Ni等の金属の単体あるいはそれらの合金がある。金属反射層は、一層だけでもよいが、リードフレームに実装するときの耐ハンダ性、耐熱性や耐ボンディング性を向上せしめるためにNi、W、Mo等の高融点の金属を積層した構造とすることも好ましいものとなる。

【0014】本発明におけるリードフレームの形状は素子チップをリード部材に固定するための接続部と、素子チップのそれぞれの部位に電圧を印加するための各電極と他のリード部材をワイヤーによってそれぞれ接続できる構造であればよく発光素子チップの電極形状により変えることができる。リードフレームは発光を有効に集光するためにミラー面を設けることが望ましい。

【0015】本発明における発光素子チップをリード部材にダイボンディングを行う際の接着の材料としては、一般的に使われているものが使用できる。例えばAu-Si、Pb-Sn合金系ハンダや、このハンダに少量のBi、Sb、Ag、Cd、Zn、In等の金属を添加したもの、BiにNa、Tl、Cd、Sn、Pb等を添加し合金化したもの、InにZn、Cd、Sn、Bi等を添加し合金化したもの、GaにAg、Zn、Sn、In等を添加し合金化したもの、Au、Al、In、Ag等の金属あるいはAg、Au、Cu等を含んだ導電性ペーストがある。素子チップとリード部材とを接着する方法としては、従来のダイボンディング装置を用いた方法がある。即ち、接着層を素子チップの該電極部、もしくはリード部材の素子チップの接着面に蒸着法、塗布法あるいはメッキ法等により形成した後、該電極部と該リード部材を密着させながらリード部材を接着材料の融点以上に加熱して接着を行う。

【0016】また本発明における発光素子チップの電極部とリード部材を配線する際にはワイヤーボンダ法を用いることが特徴である。ダイボンディング法により素子チップをリード部材に固定した後に、ワイヤーボンディング装置にセットして加熱および、あるいは超音波を印加することにより電極部とリード部材とを接続する。このとき用いるワイヤーの材料としては、Au、Ag、Cu、Al等の金属、Au-Si、Al-Si、Al-Mg、Al-Si-Mg、Al-Ni等の合金があり、どの材料を使用するかは発光素子チップの電極部の材料やワイヤーボンディングの作業性を考慮して選べばよい。なかでも、AuやAl-Siが作業性がよいということで好ましい。ワイヤーの太さは、発光素子チップの電極部の大きさやワイヤーボンディングの作業性を考慮して選べばよく、通常は20～300μmφである。また、ワイヤーの酸化を防ぐために、不活性ガス中でワイヤーボンディングを行うことも好ましい方法である。

【0017】本発明における封止材料としては発光素子チップの発光波長範囲での光透過率が80%以上の透光性材料を使用することが好ましい。この透光性材料としては、メタクリル系樹脂、エボキシ系樹脂、ポリカーボネート系樹脂、ポリスチレン系樹脂、ポレオレフィン系樹脂あるいは低融点ガラスの少なくとも一種を使用することができる。封止方法としては、たとえば所望形状の金型にこれらの透光性材料の原料または加熱溶融体を注形して金型内で固化させる方法を用いることができる。こ

の固化の方法として、モノマーやオリゴマーの熱または光による重合固化、加熱溶融体では冷却固化、化学反応等を挙げることができる。この透光性材料には必要があれば、色調調節や視感度補正のための色素、顔料、蛍光体などを、樹脂の安定化のための酸化防止剤、安定剤、成形加工のための潤滑剤、滑剤を添加することも可能である。

【0018】以上説明した各方法を用いて作製したLEDの例を図3に示すが、これに限定されるものではない。

10 素子チップ24は、絶縁基板上にn型半導体層、p型およびI型半導体から選ばれた2種以上の組み合わせからなる発光層を少なくとも一つ有し、かつそれぞれの半導体層の所定の部位に、発光層に電圧を印加するための電極を有するブレーナ構造の素子チップである。この素子チップの基板面あるいはリード部材22の接着面に蒸着法でハンダを蒸着した後、リード部材22の接着面に素子チップ24を載せハンダの融点以上に加熱して接着する。その後、各電極とそれぞれのリード部材とをワイヤーボンディング法を用いて金線により接続する。その後、透光性材料により封止してLED25を作製する。

【0019】以下、一例として絶縁性基板としてAl₂O₃を使用してMBE法を用いてGaN薄膜を成膜しLEDを作製する方法について説明するが、とくにこれに限定されるものではない。装置としては、図1に示すような真空容器1内に、蒸発用ルツボ(クードセンセル)2、3および4、ガスセル7、基板加熱ホルダー5を備えたガスソースMBE装置を使用した。

【0020】蒸発用ルツボ2にはGa金属を入れ、基板面において $10^{13} \sim 10^{14} / \text{cm}^2 \cdot \text{sec}$ になる温度に加熱した。アンモニアの導入にはガス導入管8を用い、アンモニアをガスセル7内から基板6に直接吹き付けるようにした。アンモニアの導入量は基板表面において $10^{16} \sim 10^{17} / \text{cm}^2 \cdot \text{sec}$ になるように供給した。蒸発用ルツボ3にはIn、Al等を入れ、所定の組成の化合物半導体、および所定のキャリア密度を有する半導体となるように温度および時間を制御して成膜を行なう。蒸発用ルツボ4にはMg、Zn、Be、Sb、Si、Ge、C、Sn、Hg、As、P等を入れ、所定の供給量になるように温度および供給時間を制御することによりドーピングを行ない、n型およびI型あるいはp型半導体層を成膜する。

【0021】基板6にはサファイアR面を使用し、200～900°Cに加熱した。サファイアR面基板は、オフ角が0.8度以下のものが好ましい。まず、基板6を真空容器1内で750°Cで加熱した後、各ルツボを所定の成長温度に設定し、まず蒸発用ルツボ3を開き、0.1～30オングストローム/secの成長速度で0.05～2μmの厚みのn型GaN薄膜を作製する。さらにその後、Znをチャージした蒸発用ルツボ4のシャッター

を開き、0.1~3.0オングストローム/secの成長速度で0.01~1μmの厚みでi型あるいはp型GaN薄膜を成膜して発光層を形成する。この成膜時には常にガスセルを加熱し基板表面にアンモニアを供給する。

【0022】以上のような方法で成膜した発光層を有するGaN薄膜を用いてLEDを作製する工程を図2(a)から図2(h)にしたがって説明する。真空蒸着法を用いてAl, O₂側に金属反射膜17を蒸着する(a)。GaN薄膜表面にレジストを塗布する。レジストの膜厚はエッチングしたいGaN薄膜の厚みによって変えればよく0.1~3μmとするのが好ましい。スピニコーターの条件は2500rpm, 30secである。塗布後に90℃に加熱されたクリーンオープン内で30分間プレベークする(b)。その後、素子パターン形成用マスクを用いてUV露光・現像を行った(c)。Arをガスとして用いてイオンミリング法によりi層あるいはp層のGaN薄膜14を除去する(d)。イオンミリング終了後、アセトンを用いてレジストを除去する。

【0023】なお、各工程でのイオンミリングを行う時間はエッチングを行う膜厚によって決めることができる。以上の工程の後、管状炉内に試料をセットしてアンモニアを雰囲気として500℃で30分間熱処理した。熱処理後、再度レジストを塗布し、プレベークを行い、続いてn層電極形成用マスクを用いてUV露光・現像を行った後(e)、真空蒸着法によりn型GaN層15の電極としてAlを3000オングストロームの厚さに蒸着し、リフトオフにより電極パターン19を形成した(f)。ついで再度レジストを塗布し、プレベークを行い、i層電極形成用マスクを用いてUV露光・現像を行った後(g)、真空蒸着法によりp型あるいはi型GaN層14の電極としてAuを3000オングストロームの厚さに蒸着し、リフトオフにより電極パターン20を形成した(h)。その後、Ar流中で300℃、1時間の加熱処理を行った。

【0024】以上のようにして作製した発光素子チップの金属反射膜をハンダによりリード部材22に接着し、n型GaN層、i型GaN層の電極をワイヤーボンディング装置を用いて30μmのAu線23でそれぞれリード部材21、リード部材22にボンディングした。その後、発光素子チップを透明エポキシ樹脂によりモールディングを施し、図3に示す様な5mmφLED25を作製した。

【0025】

【実施例】以下、実施例によりさらに詳細に説明する。

【0026】

【実施例1】絶縁性基板としてAl, O₂, R面を使用し、MBE法によりGaN薄膜を成膜し、ミアンダ状の電極構造を有する素子チップを用いてLEDを作製した例について説明する。図1に示すような真空容器1内

に、蒸発用ルツボ2、4、ガスセル7、および基板加熱ホルダー5、さらにガスセル7にガスを供給するためのガス導入管8を備えたMBE装置を用いた。

【0027】蒸発用ルツボ2にはGaN金属を入れ、1050℃に加熱した。ガスとしてはアンモニアを使用し、ガス導入管8を通してガスセル7に5cc/minの速度で供給した。アンモニアガスは基板6に直接供給するような構造とした。基板6としては、オフ角が0.5度のサファイアR面を使用する。真空容器内の圧力は、成膜時において 2×10^{-6} Torrであった。

【0028】まず、基板6を900℃で30分間加熱し、ついで750℃の温度に保持し成膜を行う。成膜はアンモニアを300℃に加熱したガスセル7から供給しながらGaNのルツボのシャッターを開けて行い、1.5オングストローム/secの成膜速度で膜厚0.5μmのn型GaN薄膜を作製した。さらにMgをチャージして300℃に保たれた蒸発用ルツボ4のシャッターを開けMgドープのGaN薄膜を1.5オングストローム/secの成膜速度で膜厚0.05μmの厚さで成膜して発光層を形成した。この作製した薄膜のRHEEDパターンはストリーク状で結晶性および平坦性が良好であり、抵抗を測定したところ、10MΩ以上の抵抗があり絶縁状態であった。

【0029】発光層が形成されている基板面の反対面に真空蒸着法を用いて 2×10^{-6} Torrの真空中でAlを3000オングストロームの厚みで蒸着し反射膜を形成した。続いて発光層上にスピニコーターを用いて2500rpm, 30secの条件でレジストを塗布し、90℃のクリーンオープン中で30分間プレベークした。

【0030】ベーク後、素子パターン形成用のマスクを用いてUV露光し、現像した。続いて、加速電圧500V、圧力 2×10^{-4} Torrの条件のArで15分間イオンミリングを行い素子パターン形成を行った。その後、アセトンを用いてレジストを除去した。次に、再度スピニコーターを用いて2500rpm, 30secの条件でレジストを塗布し、90℃のクリーンオープン中で30分間プレベークした。ベーク後、i層除去用のマスクを用いてUV露光し、現像した。続いて、加速電圧500V、圧力 2×10^{-4} Torrの条件のAr雰囲気中で1分間イオ

ンミリングを行い不必要なi層を除去した。その後、アセトンでレジストを除去した。次いで、管状炉にセットして10cc/minのアンモニアガス流中で500℃、30分間の熱処理を行った。さらに、スピニコーターを用いて2500rpm, 30secの条件でレジストを塗布し、90℃のクリーンオープン中で30分間プレベークした。ベーク後、n型GaN層の電極形成用のマスクを用いてUV露光し、現像した。続いて、真空蒸着機に接着し 2×10^{-6} Torrの真空中でAl金属を0.2μmの厚さで真空蒸着した。その後、アセトンでリフトオフして電極パターンを形成した。ついで、i型

GaN層の電極形成用のマスクを用いてUV露光し、現像した。続いて、真空蒸着機に装着し 2×10^{-6} Torr の真空中でAu金属を $0.2 \mu\text{m}$ の厚さで真空蒸着した。その後、アセトンでリフトオフして電極パターンを形成した。この作製した発光素子をAr流中で 300°C で1時間加熱処理を行い、ミアンダ状の電極構造を有する素子チップを完成させた。作製した素子チップの側面図および上面図を図7(a)、(b)に示した。

【0030】各チップのカッティングはダイシングソーを用いて行った。1素子チップは $0.5 \text{ mm} \times 0.5 \text{ mm}$ とした。このうちの1チップを取り出し反射膜側をAgペーストによりリード部材にダイポンディングした。さらにn型GaN層電極、1型GaN層電極とそれぞれのリード部材とをワイヤーボンディング装置を用いて $30 \mu\text{m}$ φ Au線で接続した。上記の方法で作製した発光素子を透明エポキシ樹脂で封止して図8に示すようなLEDを作製した。

【0031】同様の方法で100個のLEDを作製したところ、99個のLEDで発光が確認された。このLEDの発光強度を測定したところ 8V 、 20mA で 60mcd であり、青色の発光が観測された。

【0032】

【比較例1】実施例1と同様の方法によりAl₂O₃基板上に成膜した発光層を有するGaN薄膜を用いて素子化を行った。素子作製過程も実施例1と同様の方法により行い、n型GaN層、1型GaN層の両電極ともAgペーストにより、リード部材にダイポンディングを行った後、透明エポキシ樹脂で封止してLEDを作製した。同様の方法で100個のLEDを作製したところ、Agペーストにより正負の電極がつながってしまい、9個のLEDでしか発光するものは得られなかった。

【0033】

【実施例2】絶縁性基板としてAl₂O₃R面を使用し、MBE法によりGaN_xIn_{1-x}N薄膜を成膜し2色発光のLEDを作製した例について説明する。図2に示すような真空容器1内に、蒸発用ルツボ2、3、4、ガスセル7、および基板加熱ホルダー5、さらにガスセル7にガスを供給するためのガス導入管8を備えたMBE装置を用いた。

【0034】蒸発用ルツボ2にはGaN金属を入れ、 100°C に加熱し、蒸着用ルツボ3にはIn金属を入れ 1000°C に加熱した。ガスとしてはアンモニアを使用し、ガス導入管8を通してガスセル7に $5\text{cc}/\text{min}$ の速度で供給した。アンモニアガスは基板6に直接供給するような構造とした。基板6としては、オフ角が 0.5° のサファイアR面を使用する。

【0035】真空容器内の圧力は、成膜時において 2×10^{-6} Torr であった。まず、基板6を 900°C で30分間加熱し、ついで 700°C の温度に保持し成膜を行う。成膜はアンモニアを 300°C に加熱したガスセル7

から供給しながらGaNとInのルツボのシャッターを開けて行い、1.5オングストローム/secの成膜速度で膜厚 $0.5 \mu\text{m}$ のn型GaN_xIn_{1-x}N薄膜を作製した。さらにMgをチャージして 300°C に保たれた蒸発用ルツボ4のシャッターを開けMgをドーピングした1型GaN_xIn_{1-x}N薄膜を1.5オングストローム/secの成膜速度で膜厚 $0.05 \mu\text{m}$ の厚さで成膜して第1の発光層を形成した。次に基板温度を 750°C に上げて30分間温度を安定させた後、GaNのルツボのシャッターを開けて1.5オングストローム/secの成長速度で膜厚 $0.5 \mu\text{m}$ のn型GaN薄膜を成長し、さらにその上に蒸着ルツボ2および4のシャッターを開けてMgをドーピングした1型GaN薄膜を1.5オングストローム/secの成長速度で膜厚 $0.05 \mu\text{m}$ の厚さで成膜して第2の発光層を形成した。

【0036】発光層が形成されている基板面の反対面に真空蒸着法を用いて 2×10^{-6} Torr の真空中でAlを 3000 オングストロームの厚さで蒸着し反射膜を形成した。続いて、発光層上にスピンドルを用いて2500 rpm、30 secの条件でレジストを塗布し、 90°C のクリーンオープン中で30分間プレベークした。ベーク後、素子パターン形成用のマスクを用いてUV露光し、現像した。続いて、加速電圧 500V 、圧力 2×10^{-6} Torr の条件のArで25分間イオンミリングを行い素子パターン形成を行った。その後、アセトンを用いてレジストを除去した。次に、再度スピンドルを用いて2500 rpm、30 secの条件でレジストを塗布し、 90°C のクリーンオープン中で30分間プレベークした。ベーク後、フォトマスクを用いてUV露光し、現像した。続いて、加速電圧 500V 、圧力 2×10^{-6} Torr の条件のAr霧囲気中で15分間イオンミリングを行い不必要的1型GaN層、n型GaN層、1型GaN_xIn_{1-x}N層を除去した。次に、再度スピンドルを用いて2500 rpm、30 secの条件でレジストを塗布し、 90°C のクリーンオープン中で30分間プレベークした。ベーク後、フォトマスクを用いてUV露光し、現像した。ついで、加速電圧 500V 、圧力 2×10^{-6} Torr の条件のAr霧囲気中で13分間イオンミリングを行い不必要的1型GaN層、n型GaN層を除去した。さらに再度スピンドルを用いて2500 rpm、30 secの条件でレジストを塗布し、 90°C のクリーンオープン中で30分間プレベークした。ベーク後、フォトマスクを用いてUV露光し、現像した。ついで、イオンミリングを用い不必要的1型GaN層を除去した。その後、アセトンでレジストを除去した。ついで、管状炉にセットして $10\text{cc}/\text{min}$ のアンモニアガス流中で 500°C 、30分間の熱処理を行った。さらに、スピンドルを用いて2500 rpm、30 secの条件でレジストを塗布し、 90°C のクリーンオープン中で30分間プレベークした。ベーク

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後、n型GaN層およびn型Gao_{0.8}In_{0.2}N層の電極形成用のマスクを用いてUV露光し、現像した。続いて、真空蒸着機に装着し 2×10^{-6} Torrの真空中でAl金属を0.2 μmの厚さで真空蒸着した。その後、アセトンでリフトオフして電極パターンを形成した。ついで、i型GaN層およびi型Gao_{0.8}In_{0.2}N層の電極形成用のマスクを用いてUV露光し、現像した。続いて、真空蒸着機に装着し 2×10^{-6} Torrの真空中でAu金属を0.2 μmの厚さで真空蒸着した。その後、アセトンでリフトオフして電極パターンを形成した。この作製した発光素子をAr流中で300°Cで1時間加熱処理を行い、素子チップの構造を完成させた。作製した素子チップの側面図および上面図を図9(a)、(b)に示す。

【0037】各チップのカッティングはダイシングソーを用いて行った。1素子チップは1mm×1mmとした。このうちの1チップを取り出し反射膜側をPb-Snハンダでリード部材にダイボンディングした。その後n型GaN層およびn型Gao_{0.8}In_{0.2}N層の電極をワイヤーボンディング装置を用いて30 μmφAu線で接続した。さらにi型GaN層電極とリード部材、i型Gao_{0.8}In_{0.2}N層電極とリード部材とをワイヤーボンディング装置を用いて30 μmφAu線で接続した。上記の方法で作製した発光素子を透明エポキシ樹脂で封止して、図10に示すようなLEDを作製した。

【0038】同様の方法で100個のLEDを作製したところ、95個のLEDで発光が確認された。このLEDの発光強度を測定したところリード部材66とリード部材67では10V、18mAで40mcdの青色の発光が、リード部材66とリード部材68では、8V、20mAで60mcdの緑色の発光が観測された。

【0039】

【発明の効果】本発明は絶縁性基板上に発光層を形成したブレーナ型の素子チップ構造において、同一平面内に形成された全ての電極を該電極数と同じ数に分割したりード部材にワイヤーボンディング法によりワイヤーでおのの接続することで、安定した性能のLEDを供給することが可能になる。

【図面の簡単な説明】

【図1】 薄膜作製に用いたMBE装置の概略図である。

【図2】 (a)～(h) LEDの作製工程を示した断面図である。

【図3】 本発明による方法で作製したLEDの断面図である。

【図4】 ネット状電極を形成した発光素子の上面図である。

【図5】 クシ状電極を形成した発光素子の上面図である。

【図6】 ミアンダ状電極を形成した発光素子の上面図

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である。

【図7】 (a) 実施例1で作製した素子チップの断面図である。

(b) 実施例1で作製した素子チップの上面図である。

【図8】 実施例1で作製したLEDの断面図である。

【図9】 (a) 実施例2で作製した素子チップの断面図である。

(b) 実施例2で作製した素子チップの上面図である。

【図10】 実施例2で作製したLEDの断面図である。

【図11】 発光層の形成されていない側の基板面に金属層が形成された構造からなる発光素子の断面図である。

【図12】 従来の方法で作製されたLEDの断面図である。

【図13】 従来の方法で作製されたフリップチップ方式のLEDの断面図である。

【符号の説明】

1 真空容器

2 蒸発用ルツボ

3 蒸発用ルツボ

4 蒸発用ルツボ

5 基板加熱ホルダー

6 基板

7 ガスセル

8 ガス導入管

9 流量調節バルブ

10 クライオパネル

11 コールドトラップ

12 油拡散ポンプ

13 油回転ポンプ

14 p型あるいはi型半導体層

15 n型半導体層

16 絶縁性基板

17 金属反射膜

18 レジスト

19 n型半導体層電極

20 p型あるいはi型半導体層電極

21 リード部材(1)

22 リード部材(2)

23 金属ワイヤー

24 素子チップ

25 LED

26 電極

27 i型GaN層電極

28 n型GaN層電極

29 i型GaN層

30 n型GaN層

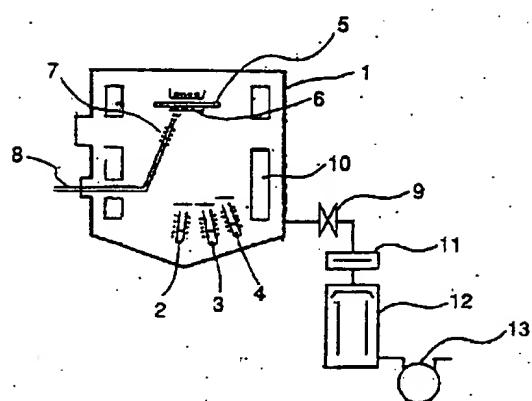
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3 1 サファイア基板
 3 2 Al反射膜
 3 3 リード部材 (3)
 3 4 リード部材 (4)
 3 5 Auワイヤー[—]
 3 6 GaN発光素子チップ
 3 7 GaN MIS型LED
 3 8 i型GaN_xIn_{1-x}N層電極
 3 9 n型GaN層およびn型GaN_xIn_{1-x}N層電極
 4 0 i型GaN_xIn_{1-x}N層
 4 1 n型GaN_xIn_{1-x}N層

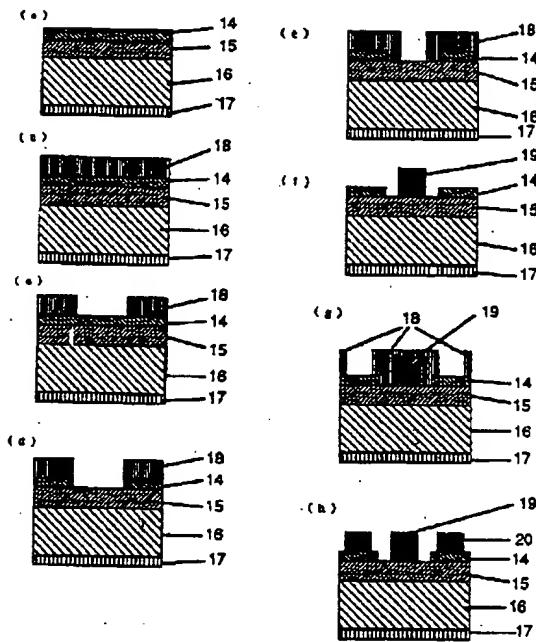
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4 2 リード部材 (5)
 4 3 リード部材 (6)
 4 4 リード部材 (7)
 4 5 GaN、GaN_xIn_{1-x}N発光素子チップ
 4 6 2色発光LED
 4 7 リード部材 (8)
 4 8 リード部材 (9)
 4 9 リードフレーム
 5 0 ミラー面
 10 5 1 リード部材 (10)
 5 2 リード部材 (11)

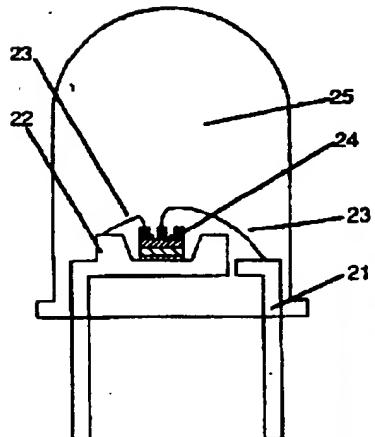
【図1】



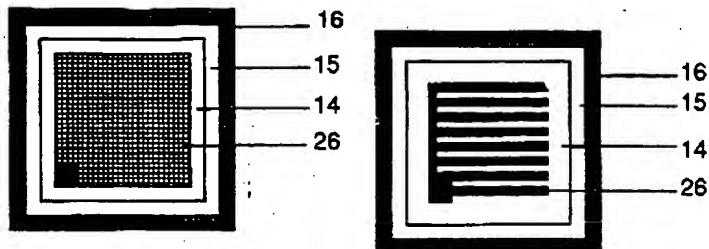
【図2】



【図3】

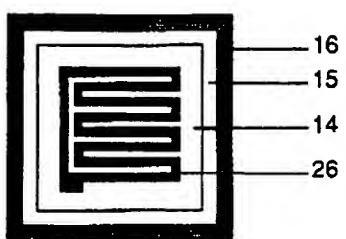


【図4】

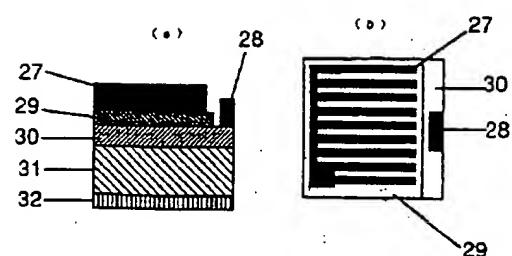


【図5】

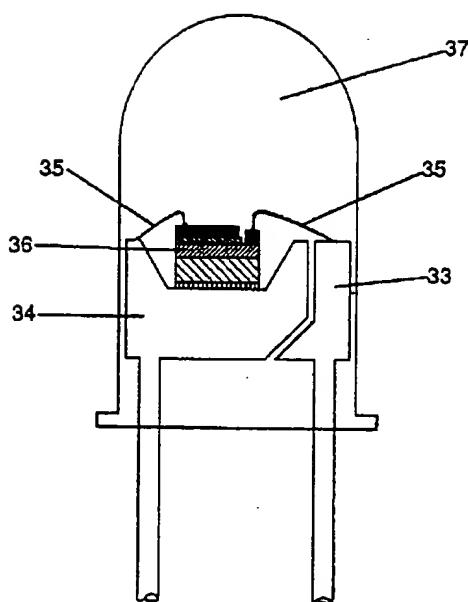
【図6】



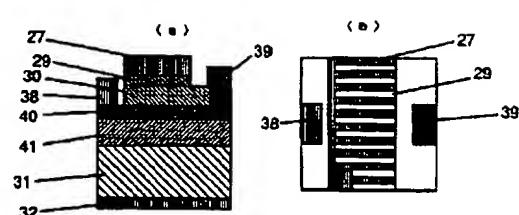
【図7】



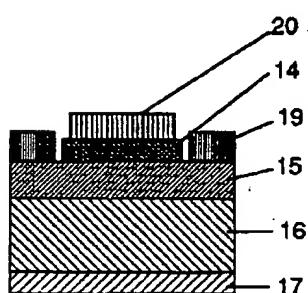
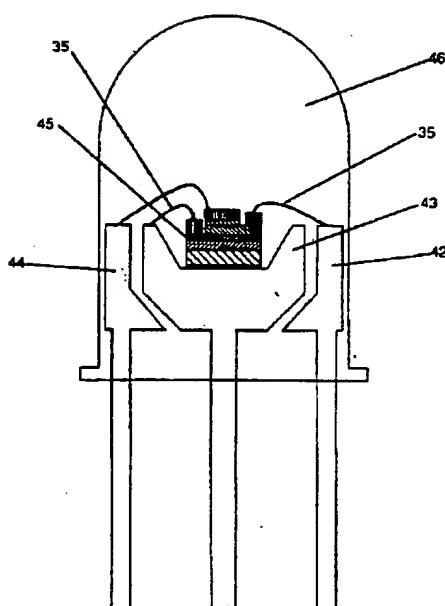
【図8】



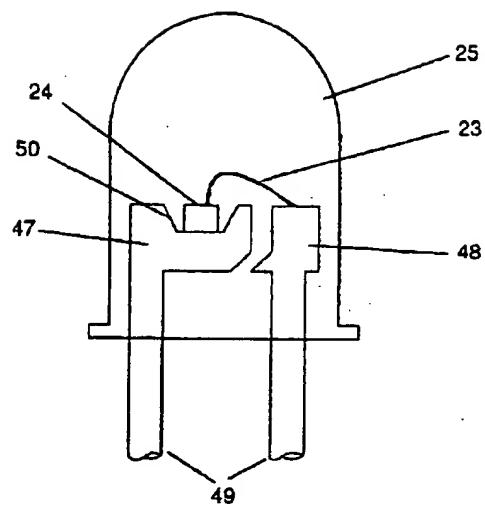
【図9】



【図10】



【図12】



【図13】

